

Automotive IPD Series

5ch Low Side Switch with Built-in LDO

BD5LL20AEFV-C

General Description

BD5LL20AEFV-C is 5-channel SPI-input low side switch developed as engine control. It has built-in open load detection function, over current protection function, thermal shutdown function, and active clamp function. It also has a 5 V output LDO as a power supply for the microcontroller and a built-in K-LINE communication circuit, making it suitable for motorcycle engine control.

Features

- AEC-Q100 Qualified^(Note 1)
 - Monolithic Power Management IC with Control Block (CMOS) and a Power MOSFET mounted on a Single Chip
 - Each Channel Control/Error can be detected by 16 bit SPI Commands
 - Built-in Open Load Detection Function (OLD)
 - Built-in Over Current Protection Function (OCP)
 - Built-in Thermal Shutdown Function (TSD)
 - Built-in Active Clamp Function
 - Built-in 5 V Output LDO
 - Built-in K-LINE Communication Circuit
 - Surface-mount HTSSOP-B20 Packaging
- ^(Note 1) Grade 1

Application

- Driving Resistive and Inductive Load

Key Specifications

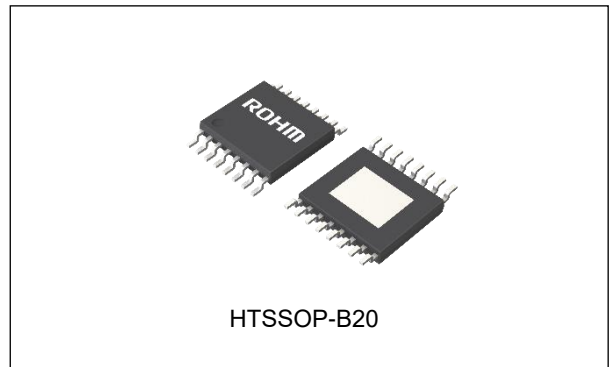
- Power Supply Operating Range VX: 6 V to 18 V
 - Power Supply Operating Range VS: 6 V to 8 V
 - LDO Output Voltage: 5.0 V (Typ)
 - LDO Over Current Threshold Value: 250 mA (Min)
 - On Resistance^(Note 1): 200 mΩ / 540 mΩ (Typ)
 - Over Current Threshold Value: 2.0 A / 0.5 A (Min)
 - Active Clamp Energy^(Note 1): 300 mJ / 250 mJ
 - Operating Temperature Range: -40 °C to +150 °C
- ^(Note 1) (OUT1, OUT2, OUT3) / (OUT4, OUT5) value

Package

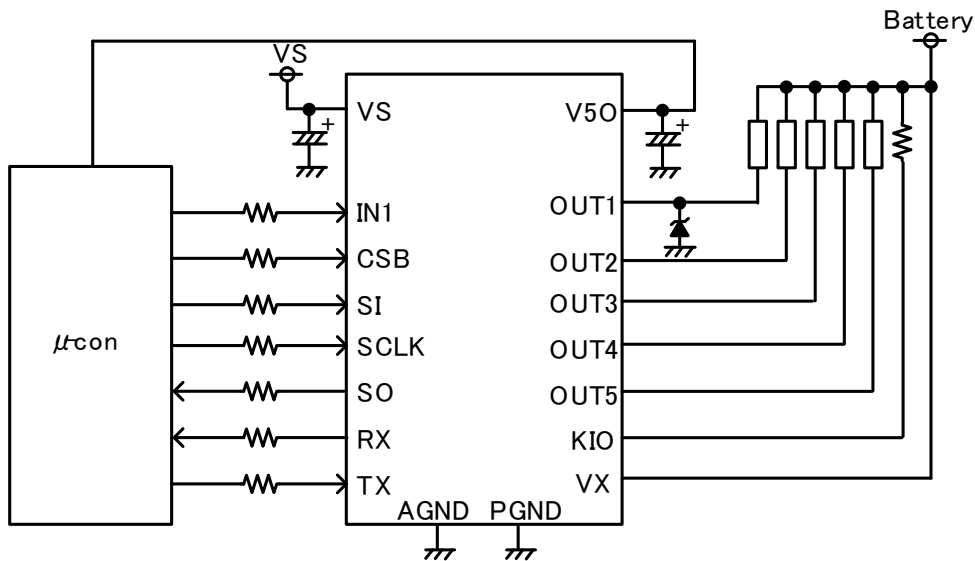
HTSSOP-B20

W (Typ) x D (Typ) x H (Max)

6.5 mm x 6.4 mm x 1.0 mm



Typical Application Circuit



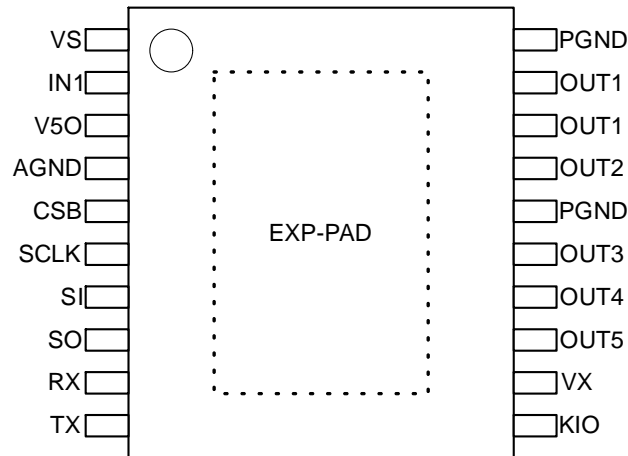
○Product structure : Silicon integrated circuit ○This product has no designed protection against radioactive rays.

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Pin Configuration

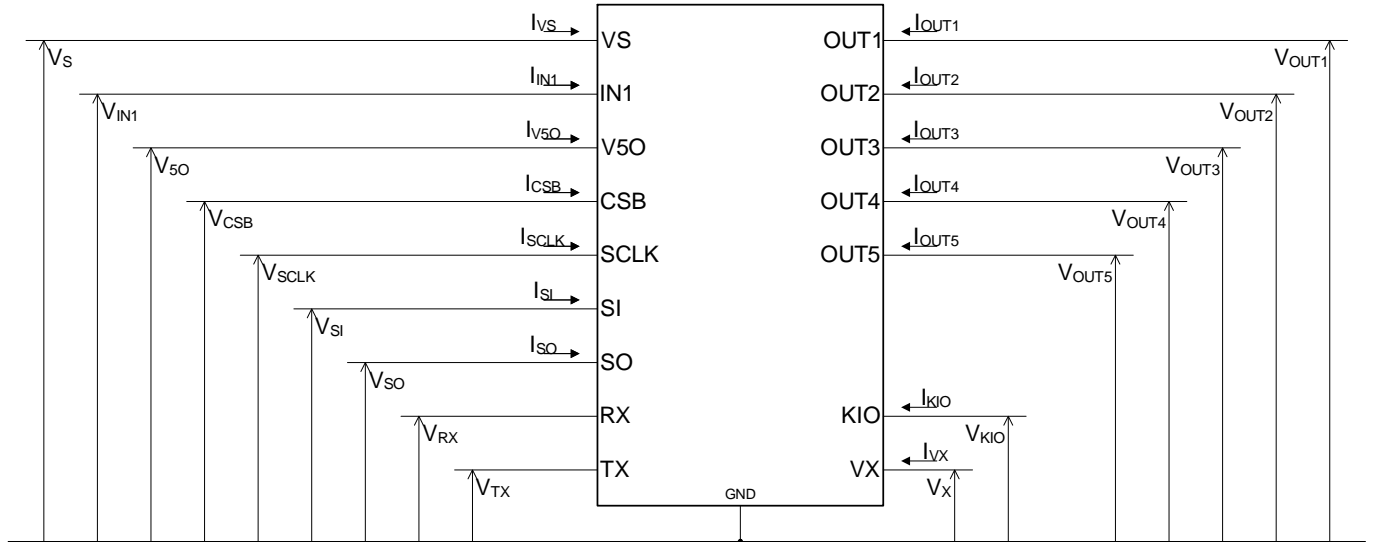
(TOP VIEW)



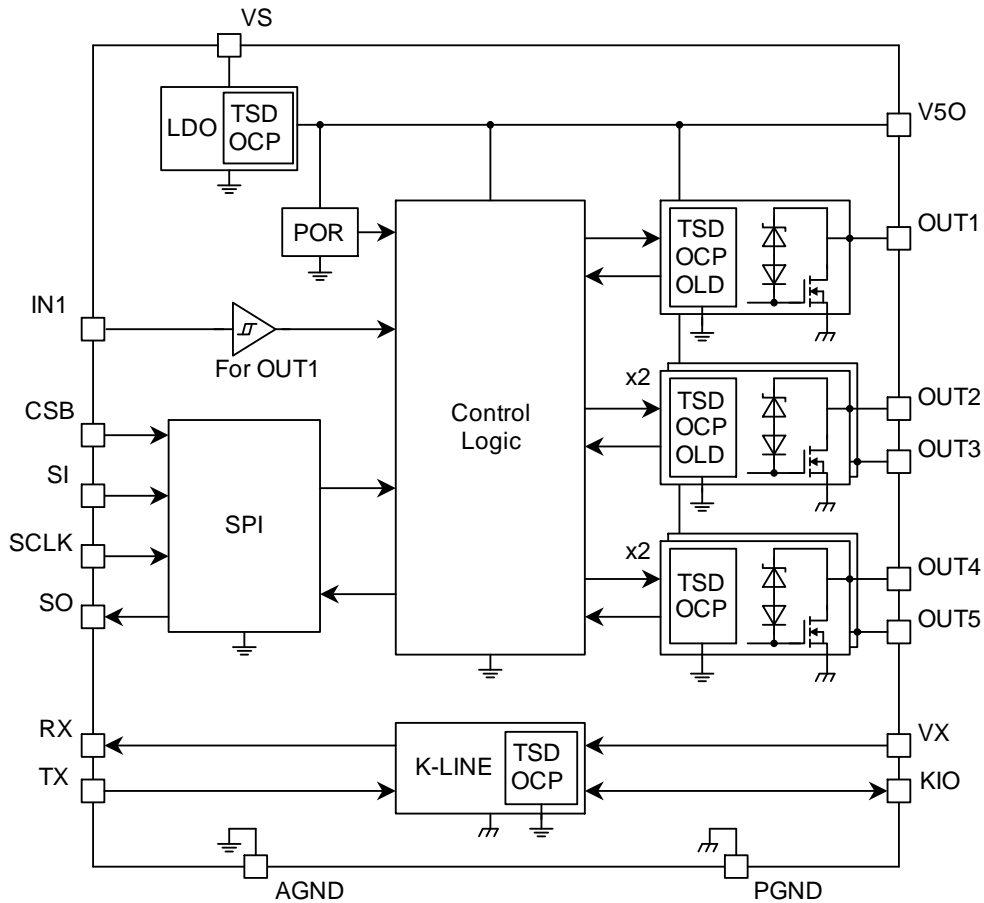
Pin Descriptions

| Pin No. | Pin Name | Function |
|---------|----------|--|
| 1 | VS | LDO power supply |
| 2 | IN1 | OUT1 control input Connected to GND via an internal pull-down resistor. |
| 3 | V5O | 5 V output |
| 4 | AGND | Analog GND |
| 5 | CSB | SPI enable Connected to V5O via an internal pull-up resistor. |
| 6 | SCLK | Serial clock input Connected to GND via an internal pull-down resistor. |
| 7 | SI | Serial data input Connected to GND via an internal pull-down resistor. |
| 8 | SO | Serial data output |
| 9 | RX | K-LINE output |
| 10 | TX | K-LINE input Connected to V5O via an internal pull-up resistor. |
| 11 | KIO | K-LINE bus connection |
| 12 | VX | K-LINE power supply |
| 13 | OUT5 | ch5 output |
| 14 | OUT4 | ch4 output |
| 15 | OUT3 | ch3 output |
| 16 | PGND | Power GND |
| 17 | OUT2 | ch2 output |
| 18 | OUT1 | ch1 output |
| 19 | OUT1 | ch1 output |
| 20 | PGND | Power GND |
| - | EXP-PAD | The EXP-PAD is connected to GND. |

Definition



Block Diagram



Absolute Maximum Ratings (Tj = 25 °C)

| Parameter | Symbol | Rating | Unit |
|---|--|--|------|
| VX Power Supply Voltage | V _X | -0.3 to +30 | V |
| VS Power Supply Voltage | V _S | -0.3 to +10 | V |
| Output Voltage OUT1, OUT2, OUT3, OUT4, OUT5 | V _{OUT1-5} | -0.3 to +30 (Internal Limit) ^(Note 1) | V |
| Output Current OUT1, OUT2, OUT3 | I _{OUT123} | 2.0 (Internal Limit) ^(Note 2) | A |
| Output Current OUT4, OUT5 | I _{OUT45} | 0.5 (Internal Limit) ^(Note 2) | A |
| Output Voltage SO | V _{SO} | -0.3 to +7 | V |
| Output Voltage RX | V _{RX} | -0.3 to +7 | V |
| Input Voltage CSB, SI, SCLK | V _{CSB} , V _{SCLK} , V _{SI} | -0.3 to +7 | V |
| Input Voltage IN1, TX | V _{IN1} , V _{TX} | -0.3 to +7 | V |
| Input Voltage KIO | V _{KIO} | -0.3 to +30 | V |
| Maximum Junction Temperature | T _{jmax} | 150 | °C |
| Storage Temperature Range | T _{stg} | -55 to +150 | °C |
| Active Clamp Energy (Single Pulse) OUT1, OUT2, OUT3, T _{j(START)} = 25 °C, I _{OUT1(START)} = 1.0 A | E _{AS123(25 °C)} | 300 | mJ |
| Active Clamp Energy (Single Pulse) OUT1, OUT2, OUT3, T _{j(START)} = 150 °C, I _{OUT1(START)} = 1.0 A | E _{AS123(150 °C)} | 75 | mJ |
| Active Clamp Energy (Single Pulse) OUT4, OUT5 T _{j(START)} = 25 °C, I _{OUT2(START)} = 0.5 A | E _{AS45(25 °C)} | 250 | mJ |
| Active Clamp Energy (Single Pulse) OUT4, OUT5 T _{j(START)} = 150 °C, I _{OUT2(START)} = 0.5 A | E _{AS45(150 °C)} | 50 | mJ |

(Note 1) Limited by the active clamp function.

(Note 2) Limited by the over current protection function.

Caution 1: Operating the IC over the absolute maximum ratings may damage the IC. The damage can either be a short circuit between pins or an open circuit between pins and the internal circuitry. Therefore, it is important to consider circuit protection measures, such as adding a fuse, in case the IC is operated over the absolute maximum ratings.

Caution 2: Should by any chance the maximum junction temperature rating be exceeded the rise in temperature of the chip may result in deterioration of the properties of the chip. In case of exceeding this absolute maximum rating, design a PCB with thermal resistance taken into consideration by increasing board size and copper area so as not to exceed the maximum junction temperature rating.

Caution 3: When IC is turned off with an inductive load, reverse energy has to be dissipated in the IC. This energy can be calculated by the following equation:

$$E_L = \frac{1}{2} L I_{OUT(START)}^2 \times \left(1 - \frac{V_{BAT}}{V_{BAT} - V_{OUT(CL)}} \right)$$

Where:

L is the inductance of the inductive load.

I_{OUT(START)} is the output current at the time of turning off.

V_{OUT(CL)} is the output clamp voltage.

The IC integrates the active clamp function to internally absorb the reverse energy E_L which is generated when the inductive load is turned off. When the active clamp operates, the thermal shutdown function does not work. Decide a load so that the reverse energy E_L is active clamp energy E_{AS123} (Figure 1.), E_{AS45} (Figure 2.) or under when inductive load is used.

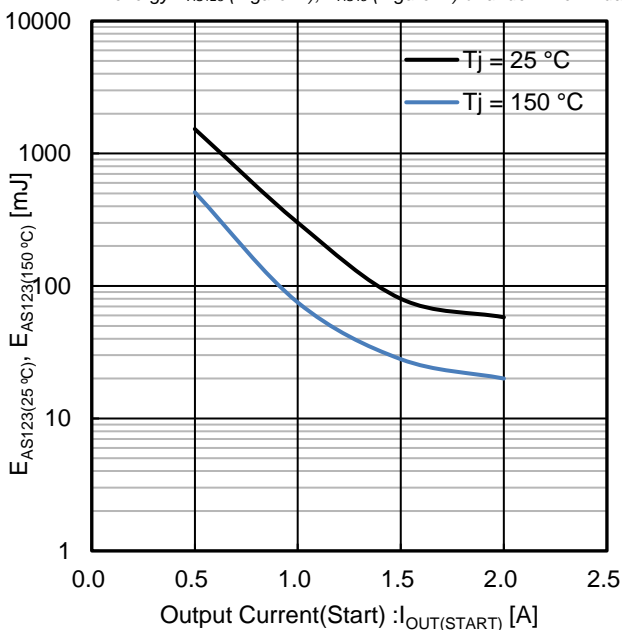


Figure 1. Active Clamp Energy (Single Pulse) vs Output Current(Start) (OUT1, OUT2, OUT3)

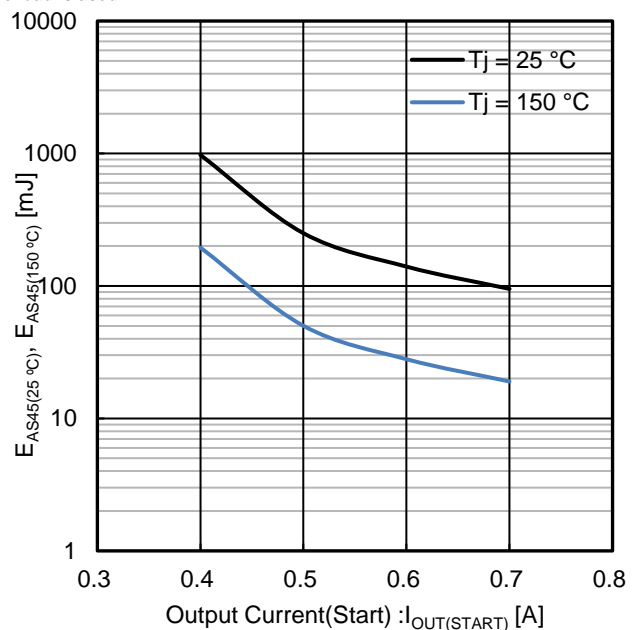


Figure 2. Active Clamp Energy (Single Pulse) vs Output Current(Start) (OUT4, OUT5)

Thermal Resistance (Note 1)

| Parameter | Symbol | Typ | Unit | Condition |
|--|---------------|------|------|---------------|
| HTSSOP-B20 | | | | |
| Between Junction and Surroundings Temperature Thermal Resistance | θ_{JA} | 95.6 | °C/W | 1s (Note 2) |
| | | 33.8 | °C/W | 2s (Note 3) |
| | | 24.4 | °C/W | 2s2p (Note 4) |

(Note 1) The thermal impedance is based on JESD51-2A(Still-Air) standard.

(Note 2) JESD51-3 standard FR4 114.3 mm x 76.2 mm x 1.57 mm 1-layer (1s)

(Top copper foil: ROHM recommended Footprint + wiring to measure, 2 oz. copper.)

(Note 3) JESD51-5 standard FR4 114.3 mm x 76.2 mm x 1.60 mm 2-layers (2s).

(Top copper foil: ROHM recommended Footprint + wiring to measure/
Copper foil area on the reverse side of PCB: 74.2 mm x 74.2 mm, copper (top & reverse side) 2 oz.)

(Note 4) JESD51-5/-7 standard FR4 114.3 mm x 76.2 mm x 1.60 mm 4-layers (2s2p)

(Top copper foil: ROHM recommended Footprint + wiring to measure/
2 inner layers and copper foil area on the reverse side of PCB: 74.2 mm x 74.2 mm, copper (top & reverse side/inner layers) 2 oz./1 oz.)

■ PCB Layout 1 layer (1s)

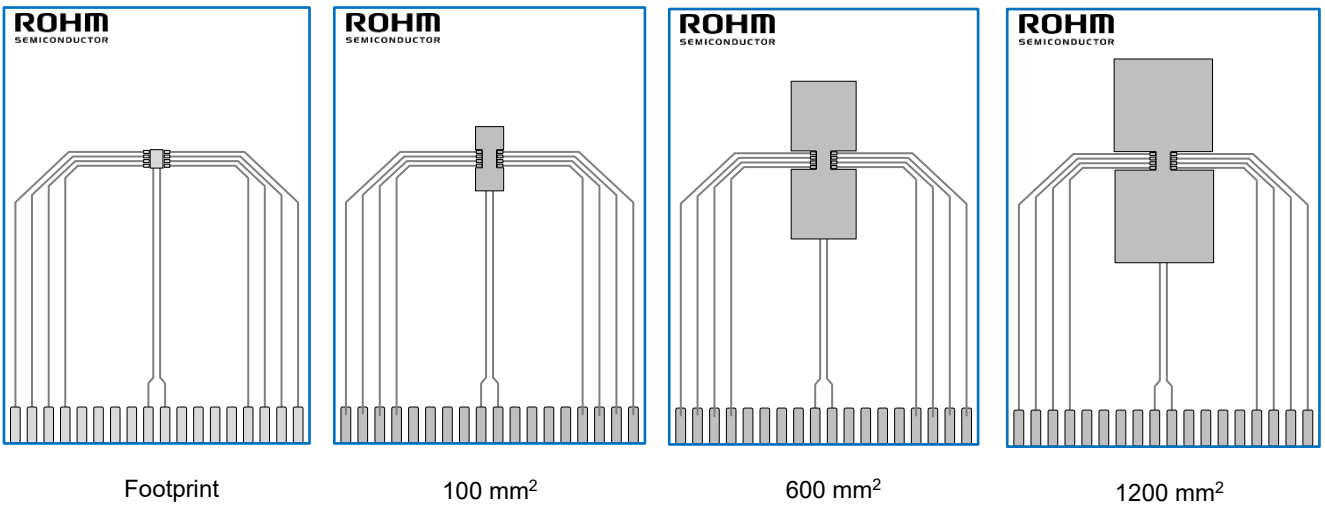


Figure 3. PCB Layout 1 Layer (1s)

| Dimension | Value |
|------------------------------|------------------------------------|
| Board Finish Thickness | 1.57 mm ± 10 % |
| Board Dimension | 76.2 mm x 114.3 mm |
| Board Material | FR4 |
| Copper Thickness (Top Layer) | 0.070 mm (Cu: 2 oz) |
| Copper Foil Area Dimension | Footprint/100 mm²/600 mm²/1200 mm² |

Thermal Resistance – continued

■ PCB Layout 2 layers (2s)

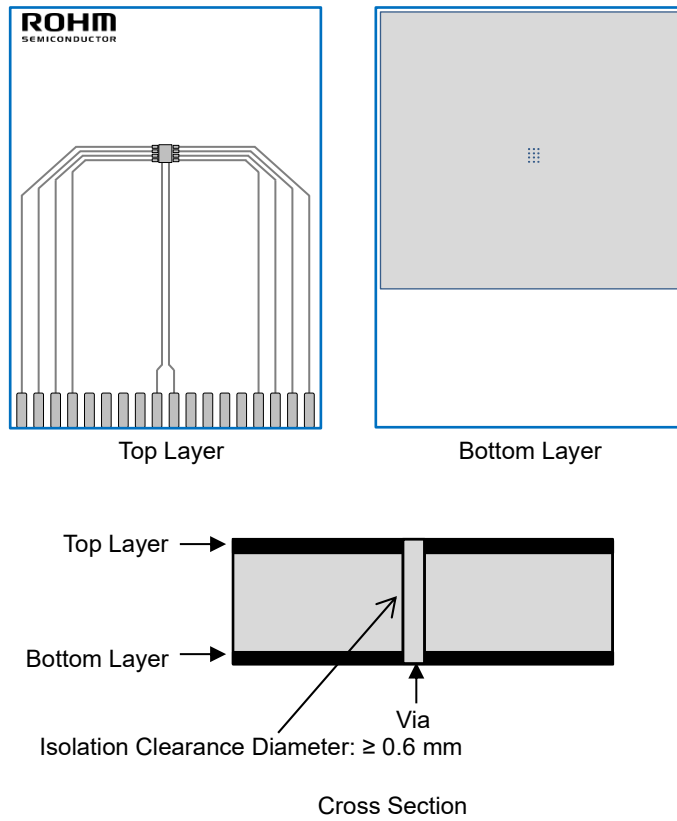


Figure 4. PCB-layout 2-layer (2s)

| Dimension | Value |
|--------------------------------------|------------------------|
| Board Finish Thickness | 1.60 mm ± 10 % |
| Board Dimension | 76.2 mm x 114.3 mm |
| Board Material | FR4 |
| Copper Thickness (Top/Bottom Layers) | 0.070 mm (Cu +Plating) |
| Thermal Vias Separation/Diameter | 1.2 mm/0.3 mm |

Thermal Resistance – continued

■ PCB Layout 4 layers (2s2p)

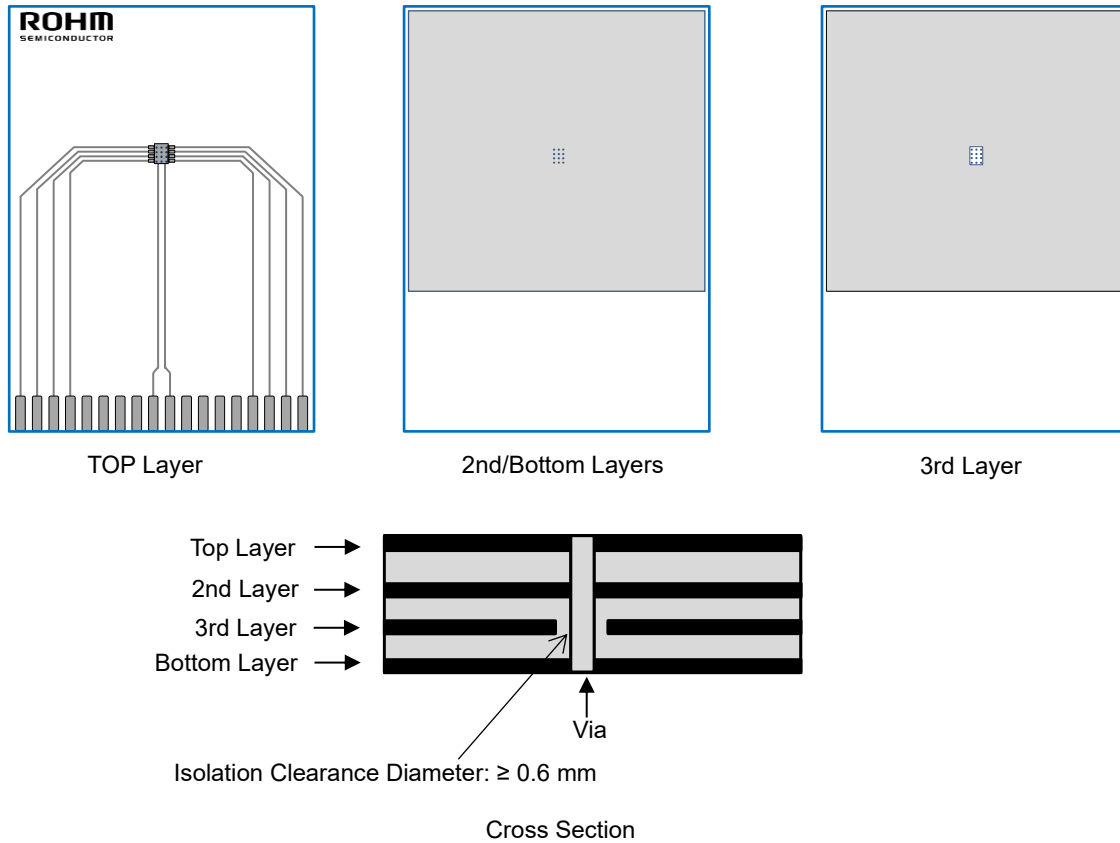


Figure 5. PCB-layout 4-layer (2s2p)

| Dimension | Value |
|--------------------------------------|------------------------|
| Board Finish Thickness | 1.60 mm \pm 10 % |
| Board Dimension | 76.2 mm x 114.3 mm |
| Board Material | FR4 |
| Copper Thickness (Top/Bottom Layers) | 0.070 mm (Cu +Plating) |
| Copper Thickness (Inner Layers) | 0.035 mm |
| Thermal Vias Separation/Diameter | 1.2 mm/0.3 mm |

Thermal Resistance – continued

■ Transient Thermal Resistance (Single Pulse)

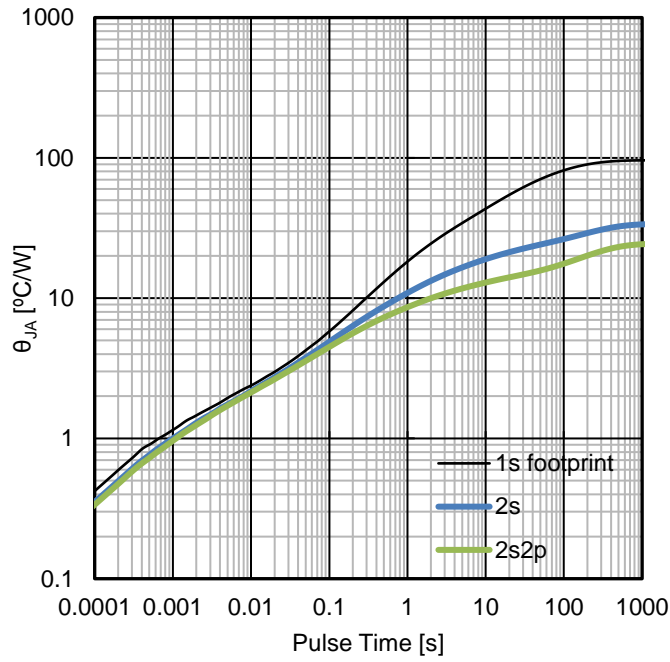


Figure 6. Transient Thermal Resistance

■ Thermal Resistance (θ_{JA} vs Copper Foil area 1s)

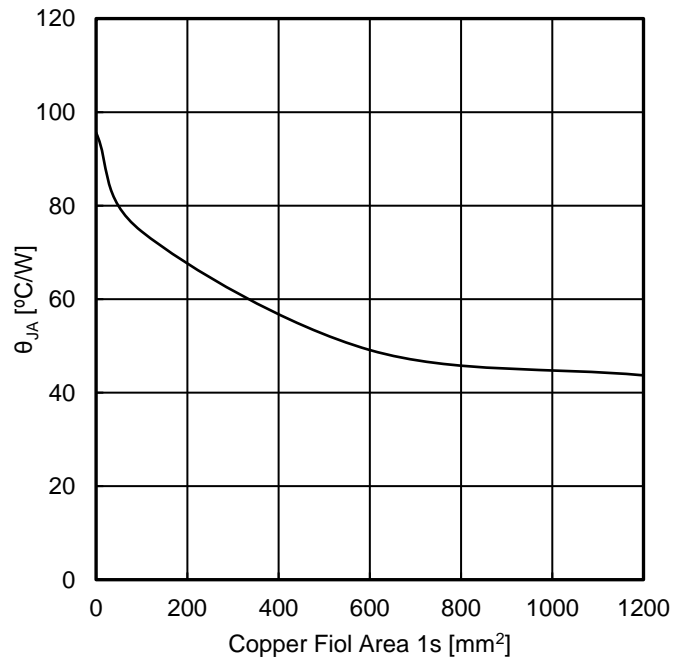


Figure 7. Thermal Resistance

Recommended Operating Conditions

| Parameter | Symbol | Min | Typ | Max | Unit |
|-------------------------|------------------|-----|------|------|------|
| VX Power Supply Voltage | V _X | 6.0 | 12.0 | 18.0 | V |
| VS Power Supply Voltage | V _S | 6.0 | 7.0 | 8.0 | V |
| Operating Temperature | T _J | -40 | +25 | +150 | °C |
| LDO Output Capacitance | C _{V50} | 68 | - | 270 | μF |

Electrical Characteristics (Unless otherwise specified V_X = 6 V to 18 V, V_S = 6V to 8V, T_J = -40 °C to 150 °C)

| Parameter | Symbol | Min | Typ | Max | Unit | Conditions |
|--|------------------------|-----------------------|-----------------------|-----------------------|------|--|
| VS Circuit Current | I _{VS} | - | 3.0 | 6.0 | mA | V _{IN1} = 0 V |
| LDO | | | | | | |
| V50 Output Voltage | V ₅₀ | 4.9 | 5.0 | 5.1 | V | 1 mA < I _{V50} < 250 mA |
| V50 Over Current Threshold Value | I _{OCP(V50)} | 250 | 500 | - | mA | V ₅₀ = 4.5 V |
| Load Regulation | ΔV _{50-Load} | - | - | 50 | mV | 1 mA < I _{V50} < 250 mA |
| Line Regulation | ΔV _{50-Line} | - | - | 10 | mV | I _{V50} = 1 mA, 6 V < V _S < 8 V |
| Low Dropout Voltage | ΔV _{50-Drop} | - | 200 | 500 | mV | I _{V50} = 250 mA |
| Power Supply Ripple Rejection Ratio | PSRR | - | 60 | - | dB | C _{V50} = 220 μF, f = 1 kHz |
| Input (CSB, SCLK, SI, IN1) | | | | | | |
| Low Level Input Voltage | V _{IL} | 0 | - | V ₅₀ × 0.2 | V | |
| High Level Input Voltage | V _{IH} | V ₅₀ × 0.7 | - | V ₅₀ | V | |
| Input Hysteresis Voltage | V _{HYS} | 0.2 | 0.45 | 0.7 | V | |
| Low Level Input Current 1 (except CSB) | I _{IL1} | -10 | 0 | +10 | μA | V _{SCLK} , V _{SI} , V _{IN1} = 0 V |
| Low Level Input Current 2 (CSB) | I _{IL2} | -100 | -50 | -25 | μA | V _{CSB} = 0 V |
| High Level Input Current 1 (except CSB) | I _{IH1} | 25 | 50 | 100 | μA | V _{SCLK} , V _{SI} , V _{IN1} = 5 V |
| High Level Input Current 2 (CSB) | I _{IH2} | -10 | 0 | +10 | μA | V _{CSB} = V ₅₀ |
| Serial Out Output | | | | | | |
| SO Low Level Output Voltage | V _{SOL} | - | 0.15 | 0.6 | V | I _{SO} = 1 mA |
| SO High Level Output Voltage | V _{SOH} | V ₅₀ - 0.6 | V ₅₀ - 0.3 | - | V | I _{SO} = -1 mA |
| Serial Out Output Leakage Current | I _{SO(OFF)} | -5 | 0 | +5 | μA | V _{SO} = 0 V / 5 V |
| Power MOS Output OUT1, OUT2, OUT3 | | | | | | |
| Output On Resistance | R _{DS(ON)123} | - | 200 | 250 | mΩ | I _{OUT} = 1 A, T _J = 25 °C |
| | | - | 300 | 375 | mΩ | I _{OUT} = 1 A, T _J = 150 °C |
| Output Sink Current During OLD | I _{OLD} | 15 | 40 | 90 | μA | V _{OUT} = 24 V |
| Turn-On Time | t _{ON123} | - | 6 | 12 | μs | R _L = 24 Ω, V _{BAT} = 12 V |
| Turn-Off Time | t _{OFF123} | - | 6 | 12 | μs | R _L = 24 Ω, V _{BAT} = 12 V |
| Slew Rate (On) | SR _{ON123} | 1.3 | 2.5 | 4.0 | V/μs | R _L = 24 Ω, V _{BAT} = 12 V |
| Slew Rate (Off) | SR _{OFF123} | 2.0 | 3.5 | 6.0 | V/μs | R _L = 24 Ω, V _{BAT} = 12 V |
| Output Clamp Voltage | V _{CL123} | 30 | 35 | 40 | V | I _{OUT} = 1 mA (Output Off) |
| Power MOS Output OUT1, OUT2, OUT3 Protection Circuit | | | | | | |
| Over Current Threshold Value | I _{OCP123} | 2 | 3.5 | 5.5 | A | |
| Over Current Detection Time | t _{OCP123} | 22 | 45 | 90 | μs | |
| Open Load Detection Release Voltage | V _{OLD(OFF)} | 1.2 | 2.5 | 3.5 | V | Output Off Setting |
| Open Load Detection Detect Voltage | V _{OLD(ON)} | 1.0 | 2.0 | 3.1 | V | Output Off Setting |
| Output Overhead Detection Detect Voltage | V _{OFD(ON)} | 1.2 | 2.5 | 3.5 | V | Output On Setting |
| Output Overhead Detection Release Voltage | V _{OFD(OFF)} | 1.0 | 2.0 | 3.1 | V | Output On Setting |

Electrical Characteristics – continued (Unless otherwise specified $V_x = 6\text{ V to }18\text{ V}$, $V_s = 6\text{ V to }8\text{ V}$, $T_j = -40\text{ }^\circ\text{C to }150\text{ }^\circ\text{C}$)

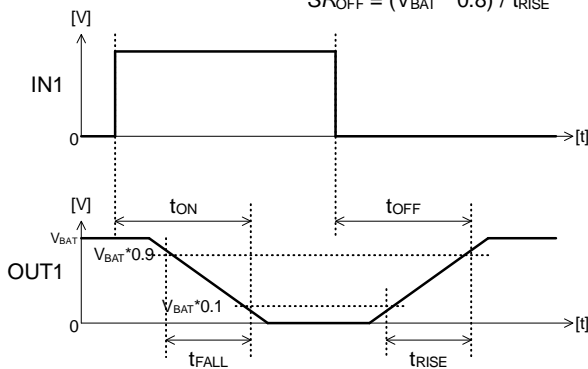
| Parameter | Symbol | Min | Typ | Max | Unit | Conditions |
|--|----------------|---------------------|------|---------------------|------|--|
| Power MOS Output OUT4, OUT5 | | | | | | |
| Output On Resistance | $R_{DS(ON)45}$ | - | 540 | 675 | mΩ | $I_{OUT} = 0.2\text{ A}$, $T_j = 25\text{ }^\circ\text{C}$ |
| | | - | 880 | 1100 | mΩ | $I_{OUT} = 0.2\text{ A}$, $T_j = 150\text{ }^\circ\text{C}$ |
| Output Leakage Current | $I_{OUT(L)45}$ | - | 0 | 1 | μA | $V_{OUT} = 24\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$ |
| | | - | 0.5 | 3 | μA | $V_{OUT} = 24\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ |
| Turn-On Time | t_{ON45} | - | 15 | 25 | μs | $R_L = 60\text{ }^\Omega$, $V_{BAT} = 12\text{ V}$ |
| Turn-Off Time | t_{OFF45} | - | 30 | 50 | μs | $R_L = 60\text{ }^\Omega$, $V_{BAT} = 12\text{ V}$ |
| Slew Rate (On) | SR_{ON45} | 0.4 | 1.0 | 2.2 | V/μs | $R_L = 60\text{ }^\Omega$, $V_{BAT} = 12\text{ V}$ |
| Slew Rate (Off) | SR_{OFF45} | 0.4 | 1.0 | 2.2 | V/μs | $R_L = 60\text{ }^\Omega$, $V_{BAT} = 12\text{ V}$ |
| Output Clamp Voltage | V_{CL45} | 30 | 35 | 40 | V | $I_{OUT} = 1\text{ mA}$ (Output Off) |
| Power MOS Output OUT4, OUT5 Protection Circuit | | | | | | |
| Over Current Threshold Value | I_{OCP45} | 0.5 | 0.9 | 1.4 | A | |
| Over Current Detection Time | t_{OCP45} | 22 | 45 | 90 | μs | |
| K-LINE | | | | | | |
| VX Circuit Current | I_{VX} | - | 0.03 | 0.10 | mA | $V_{TX} = 0\text{ V}$ |
| RX Low Level Output Voltage | V_{RXL} | - | - | 0.4 | V | $I_{RX} = 1\text{ mA}$ |
| RX High Level Output Voltage | V_{RXH} | $V_{50} - 0.4$ | - | - | V | $I_{RX} = -1\text{ mA}$ |
| RX Output Delay Time | t_{RXD} | - | - | 2 | μs | |
| TX Low Level Input Voltage | $V_{IL(TX)}$ | 0 | - | $V_{50} \times 0.2$ | V | |
| TX High Level Input Voltage | $V_{IH(TX)}$ | $V_{50} \times 0.7$ | - | V_{50} | V | |
| TX Input Hysteresis Voltage | $V_{HYS(TX)}$ | 0.1 | 0.3 | 0.5 | V | |
| TX Pull-up Resistor | R_{TX} | 5 | 10 | 20 | kΩ | |
| KIO Low Level Output Voltage | $V_{KIO L}$ | - | - | 1.4 | V | $R_{KIO} = 480\text{ }^\Omega$ |
| KIO Output Leakage Current | $I_{KIO(L)}$ | - | 0 | 3 | μA | $V_{KIO} = 18\text{ V}$ |
| KIO Over Current Threshold Value | $I_{OCP(KIO)}$ | 40 | - | 140 | mA | |
| KIO Output Delay Time | t_{KIOD} | - | - | 2 | μs | $R_{KIO} = 480\text{ }^\Omega$ |

Switching Time Measurement Waveform

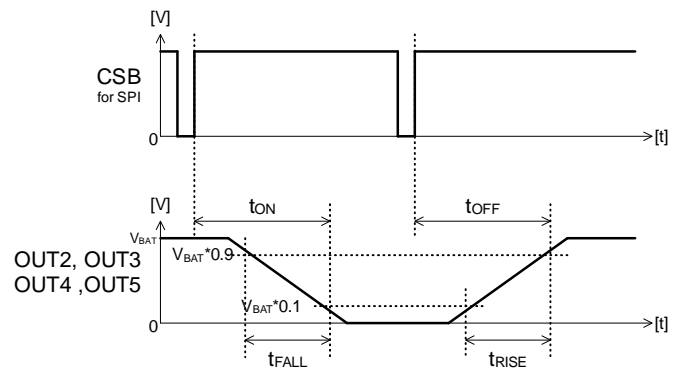
OUT1 (Control by IN1)

$$SR_{ON} = (V_{BAT} \cdot 0.8) / t_{FALL}$$

$$SR_{OFF} = (V_{BAT} \cdot 0.8) / t_{RISE}$$



OUT2, OUT3, OUT4, OUT5 (Control by SPI)



Typical Performance Curves

(Reference data) (Unless otherwise specified, $V_X = 12\text{ V}$, $V_S = 7\text{ V}$, $T_J = 25\text{ }^\circ\text{C}$)

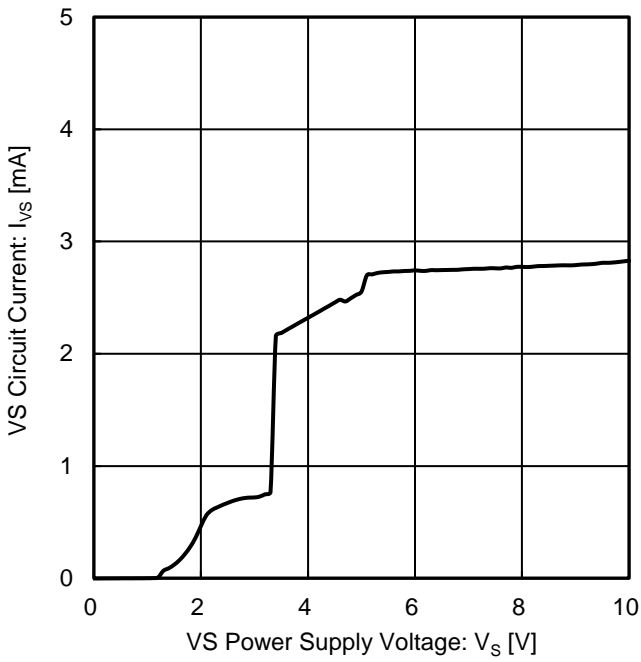


Figure 8. VS Circuit Current vs VS Power Supply Voltage

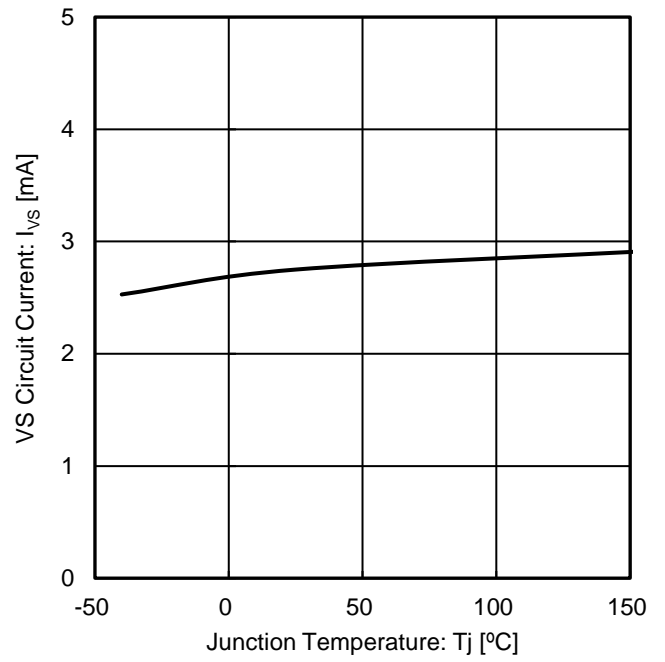


Figure 9. VS Circuit Current vs Junction Temperature

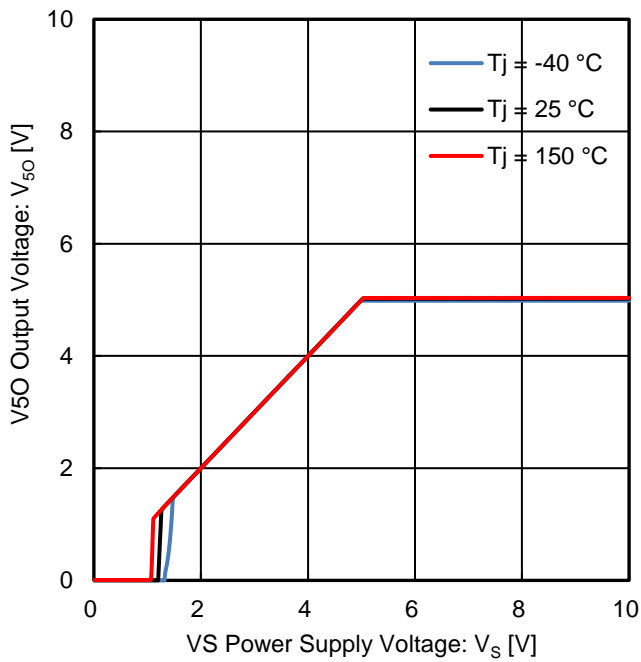


Figure 10. V5O Output voltage vs VS Power Supply Voltage

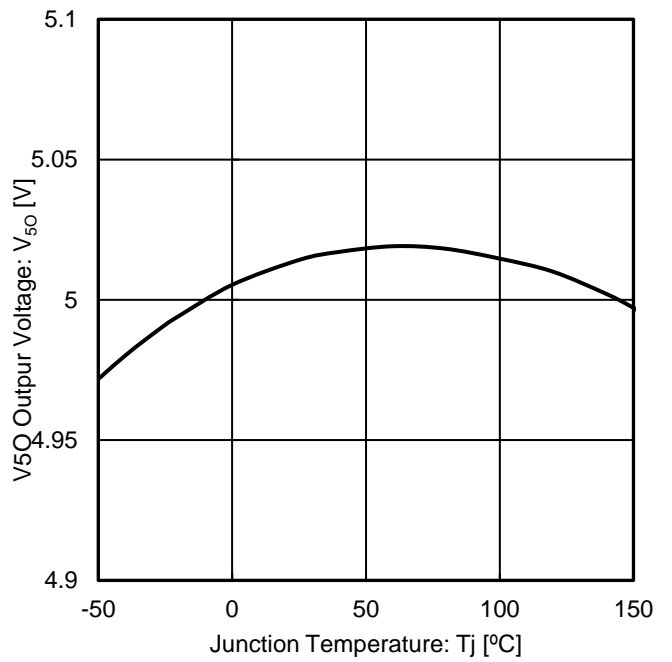


Figure 11. V5O Output voltage vs Junction Temperature

Typical Performance Curves – continued

(Reference data) (Unless otherwise specified, $V_X = 12\text{ V}$, $V_S = 7\text{ V}$, $T_J = 25\text{ }^\circ\text{C}$)

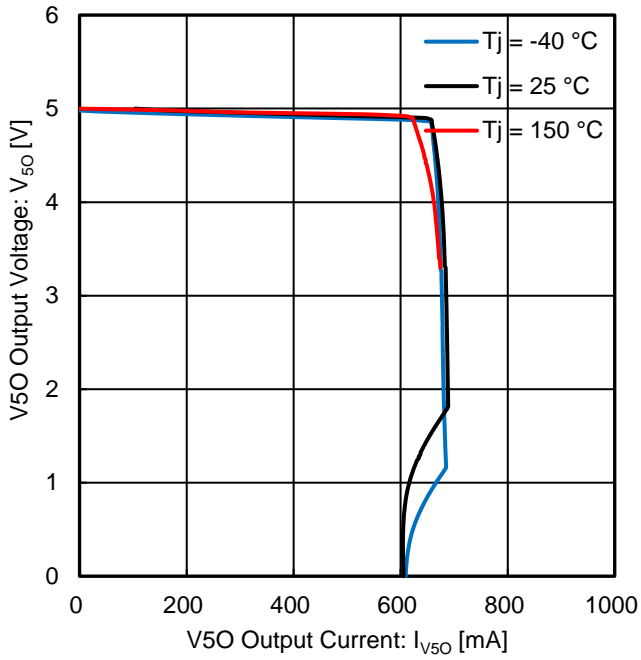


Figure 12. V5O Output voltage vs V5O Output Current

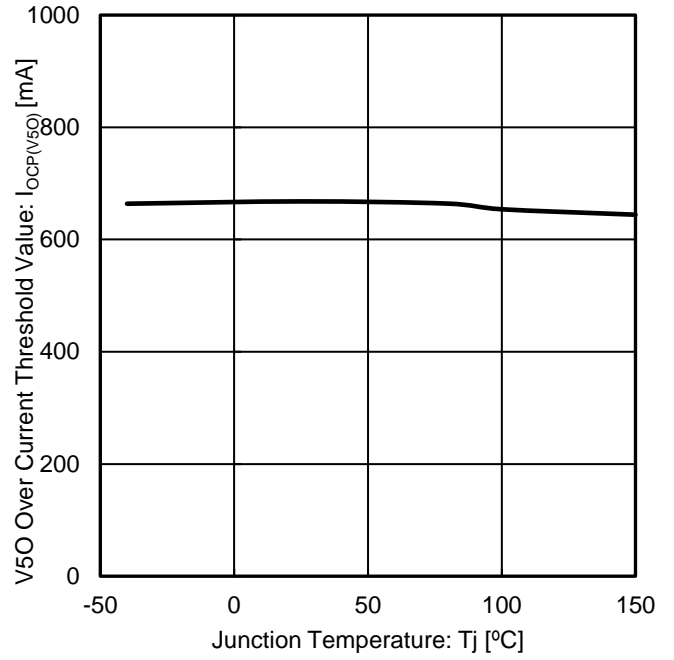


Figure 13. V5O Over Current Threshold Value vs Junction Temperature

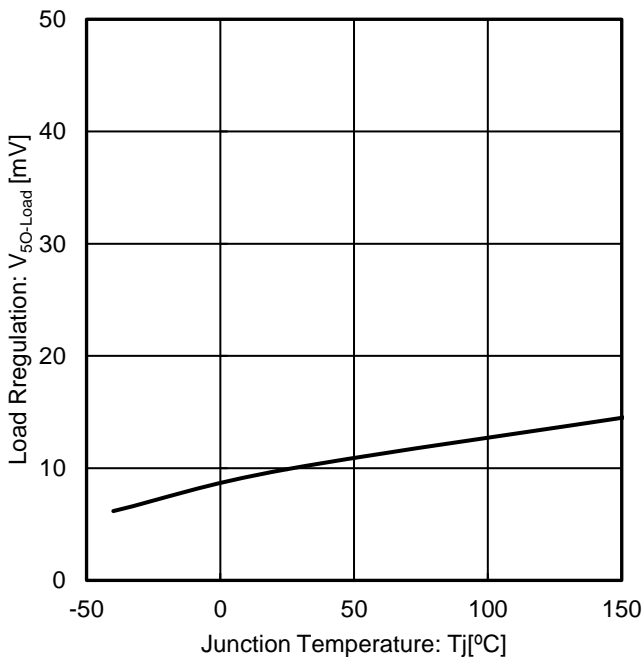


Figure 14. Load Regulation vs Junction Temperature

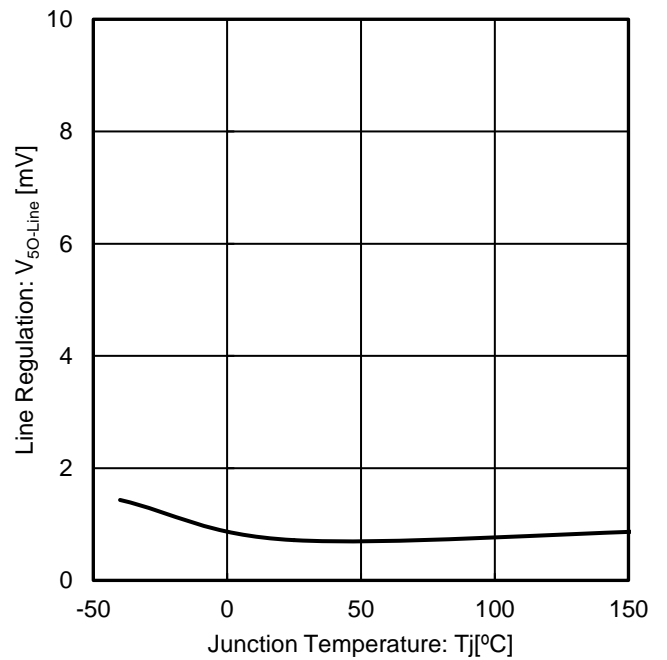


Figure 15. Line Regulation vs Junction Temperature

Typical Performance Curves – continued

(Reference data) (Unless otherwise specified, $V_X = 12\text{ V}$, $V_S = 7\text{ V}$, $T_J = 25\text{ }^\circ\text{C}$)

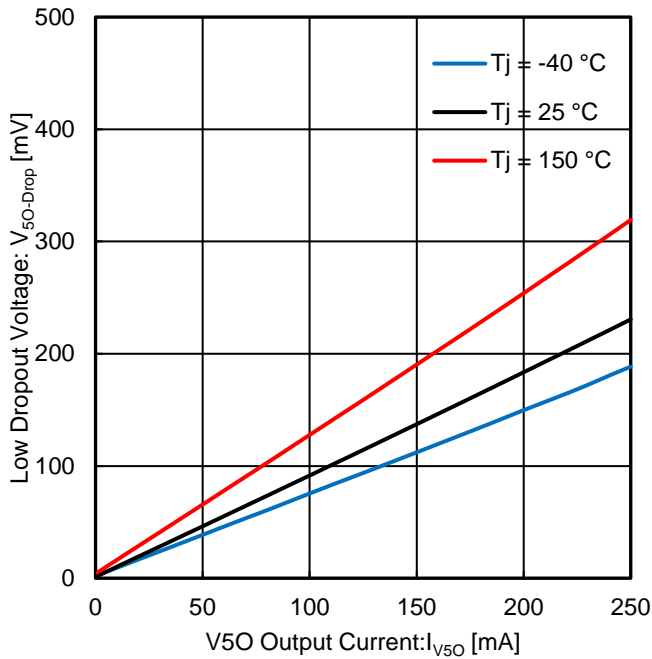


Figure 16. Low Dropout Voltage vs V50 Output Current

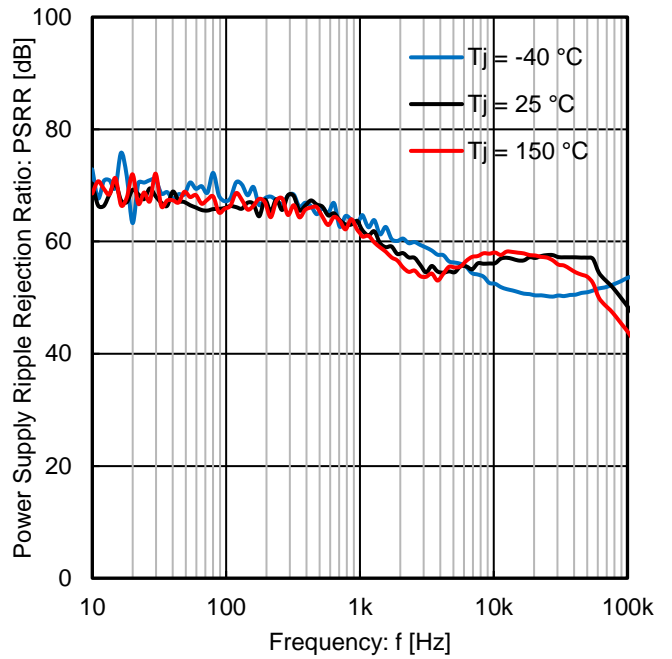


Figure 17. Power Supply Ripple Rejection Ratio vs Frequency

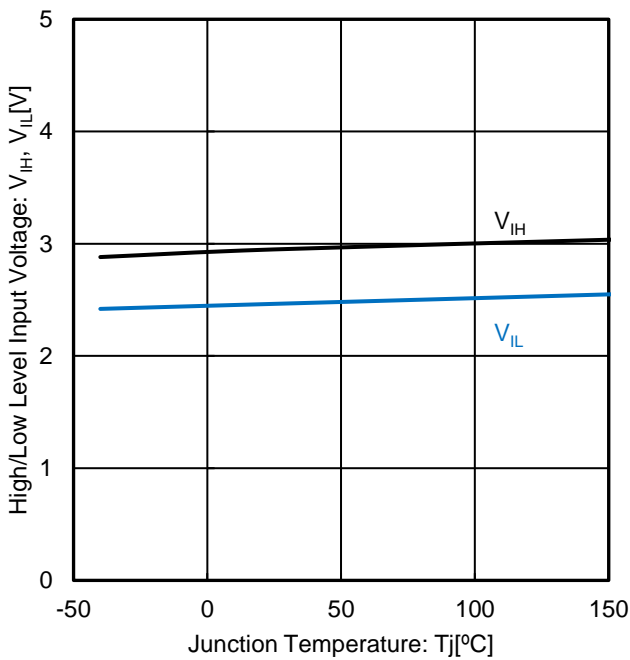


Figure 18. High Level Input Voltage / Low Level Input Voltage vs Junction Temperature

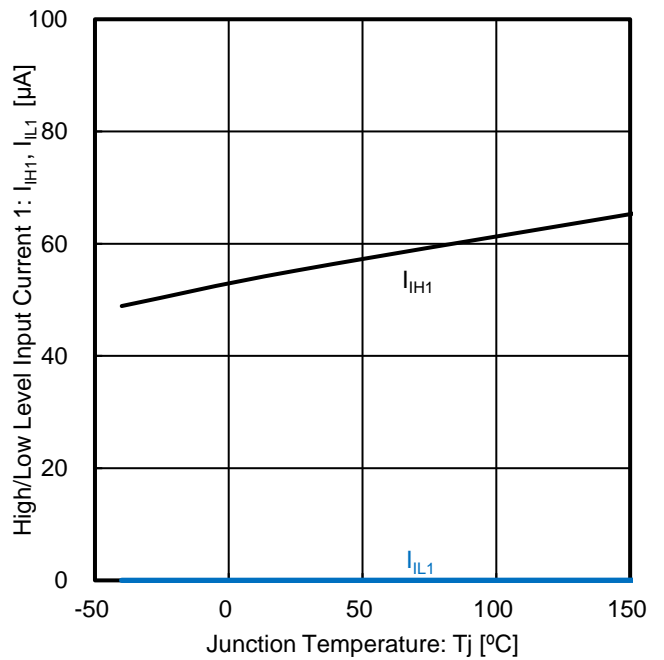


Figure 19. High Level Input Current 1 / Low Level Input Current 1 vs Junction Temperature

Typical Performance Curves – continued

(Reference data) (Unless otherwise specified, $V_X = 12\text{ V}$, $V_S = 7\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$)

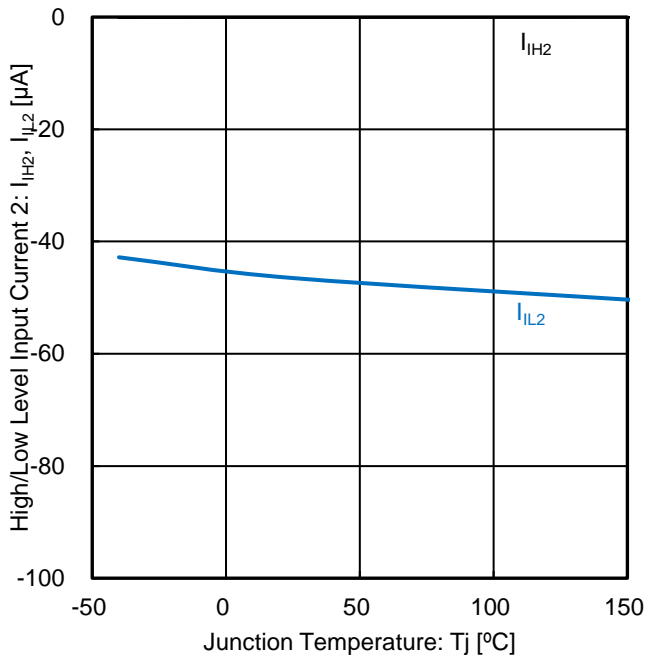


Figure 20. High Level Input Current 2 / Low Level Input Current 2 vs Junction Temperature

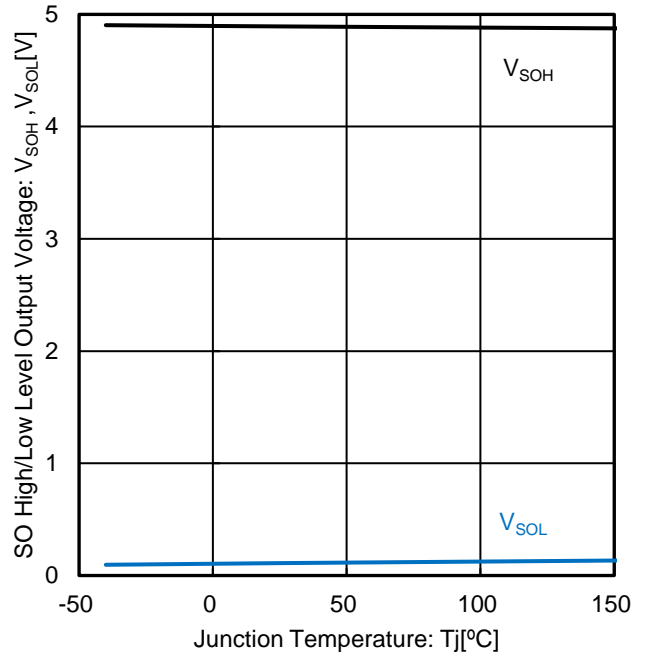


Figure 21. SO High Level Output Voltage / SO Low Level Output Voltage vs Junction Temperature

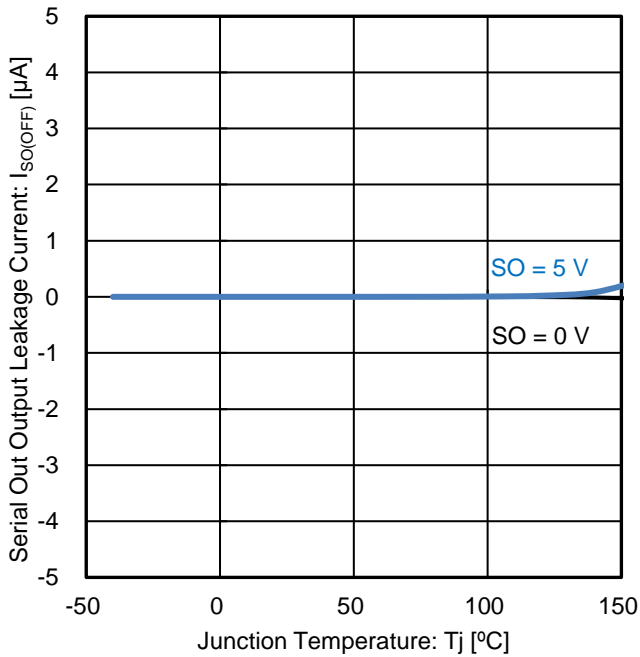


Figure 22. Serial Out Output Leakage Current vs Junction Temperature

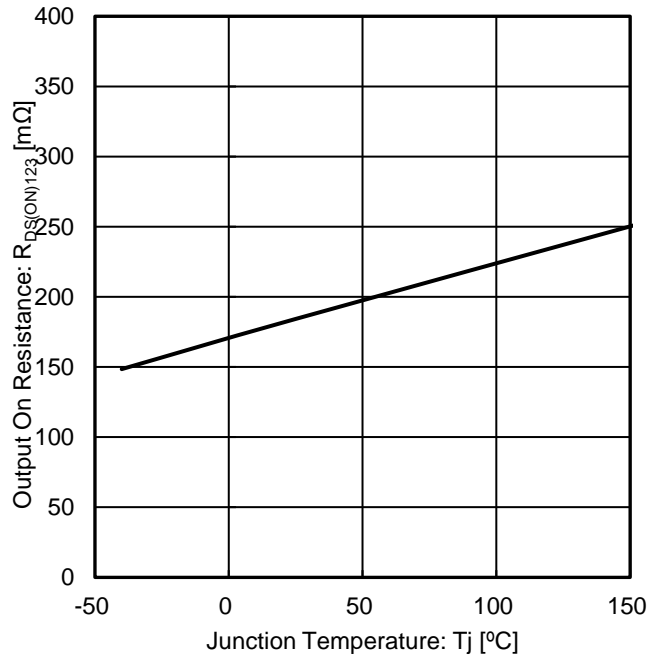


Figure 23. Output On Resistance vs Junction Temperature (OUT1, OUT2, OUT3)

Typical Performance Curves – continued

(Reference data) (Unless otherwise specified, $V_X = 12\text{ V}$, $V_S = 7\text{ V}$, $T_J = 25\text{ }^\circ\text{C}$)

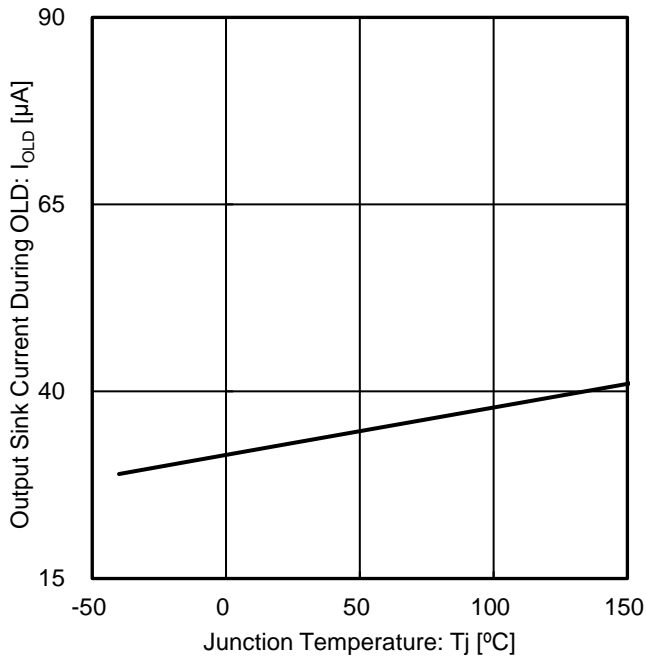


Figure 24. Output Sink Current During OLD vs Junction Temperature

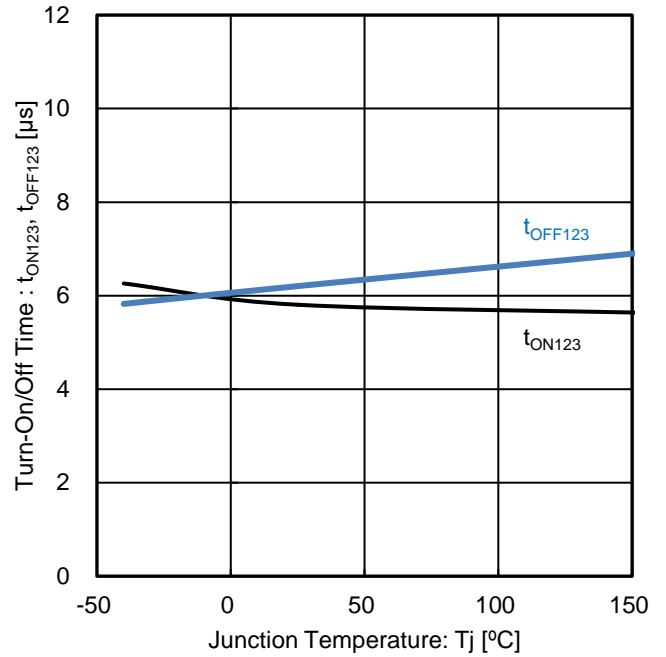


Figure 25. Turn-On Time / Turn-Off Time vs Junction Temperature (OUT1, OUT2, OUT3)

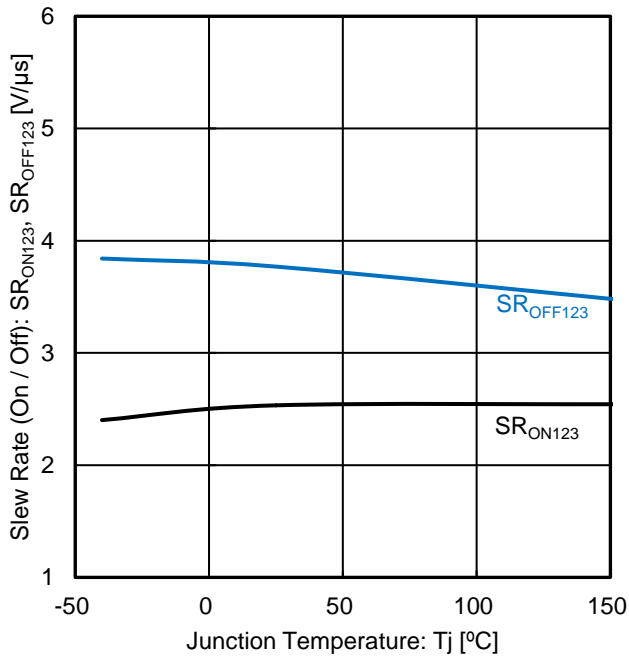


Figure 26. Slew Rate (On) / Slew Rate (Off) vs Junction Temperature (OUT1, OUT2, OUT3)

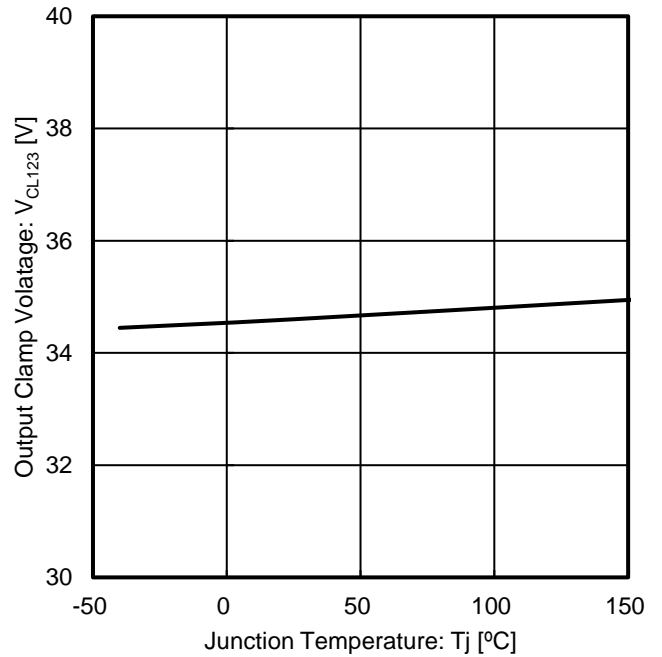


Figure 27. Output Clamp Voltage vs Junction Temperature (OUT1, OUT2, OUT3)

Typical Performance Curves – continued

(Reference data) (Unless otherwise specified, $V_X = 12\text{ V}$, $V_S = 7\text{ V}$, $T_J = 25\text{ }^\circ\text{C}$)

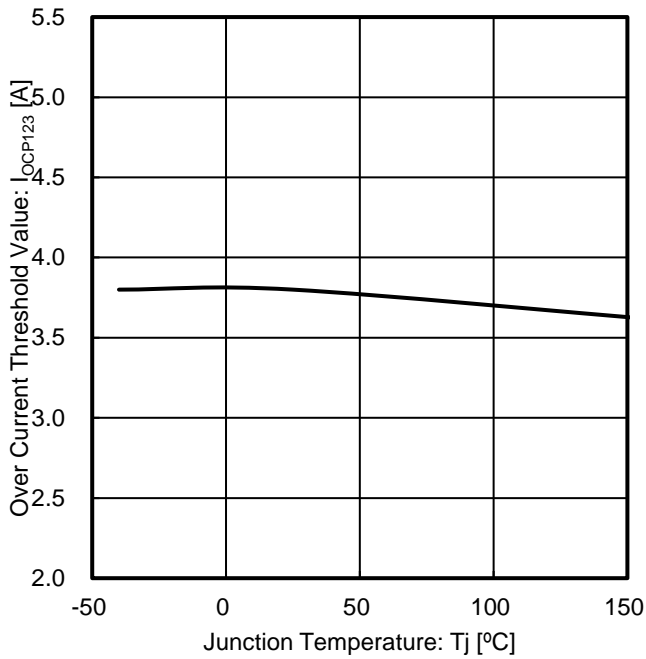


Figure 28. Over Current Threshold Value vs Junction Temperature (OUT1, OUT2, OUT3)

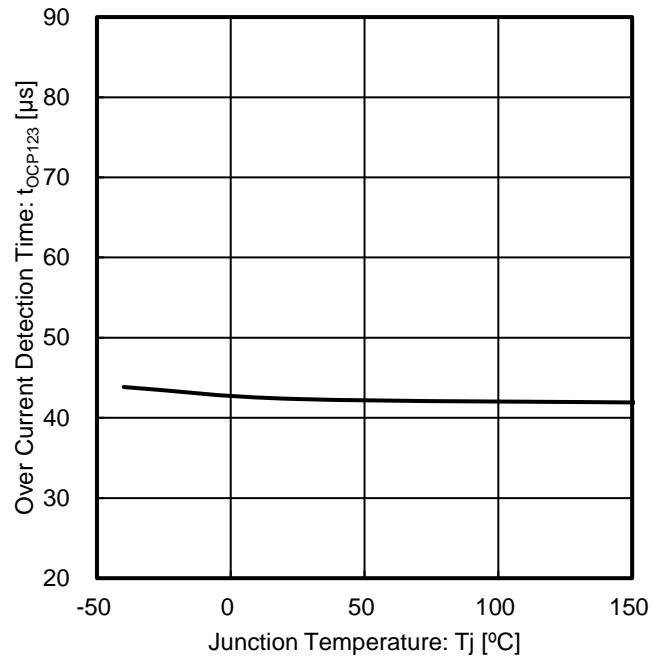


Figure 29. Over Current Detection Time vs Junction Temperature (OUT1, OUT2, OUT3)

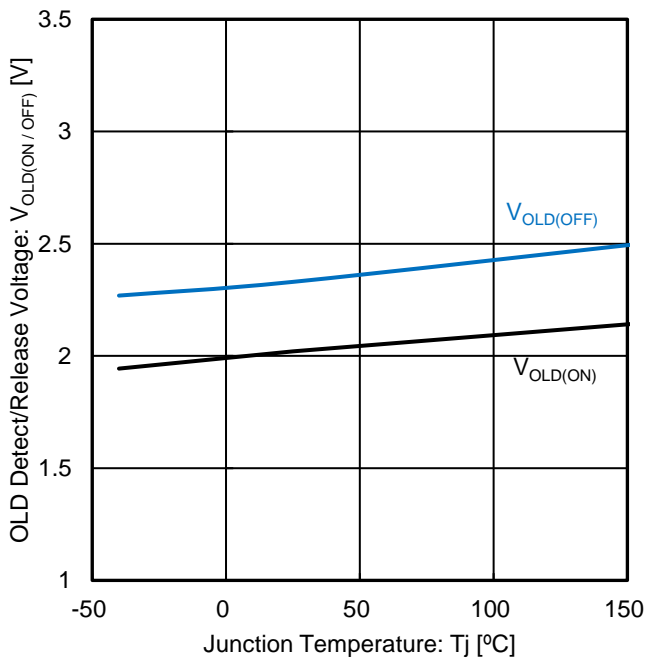


Figure 30. Open Load Detection Detect Voltage / Open Load Detection Release Voltage vs Junction Temperature

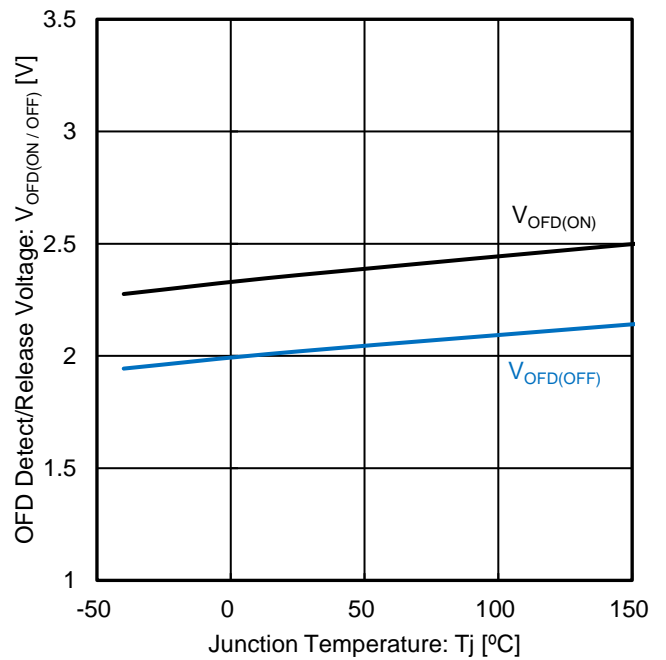


Figure 31. Output Overhead Detection Detect Voltage / Output Overhead Detection Release Voltage vs Junction Temperature

Typical Performance Curves – continued

(Reference data) (Unless otherwise specified, $V_X = 12\text{ V}$, $V_S = 7\text{ V}$, $T_J = 25\text{ }^\circ\text{C}$)

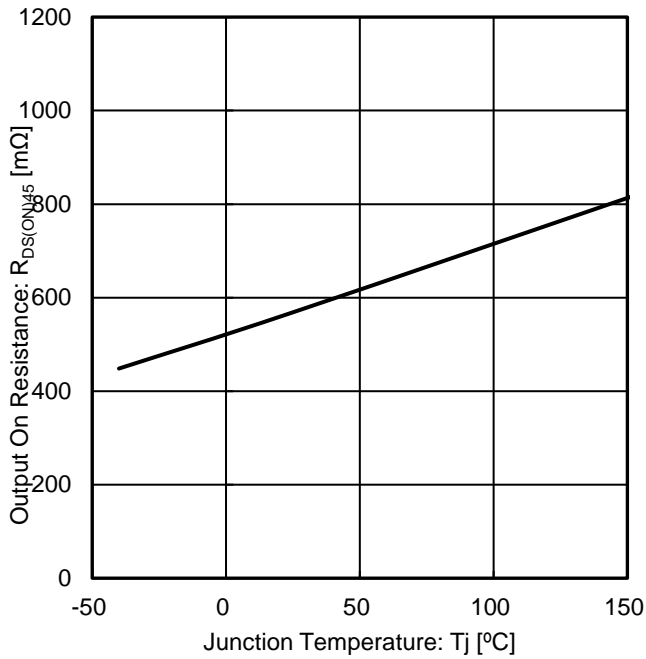


Figure 32. Output On Resistance vs Junction Temperature (OUT4, OUT5)

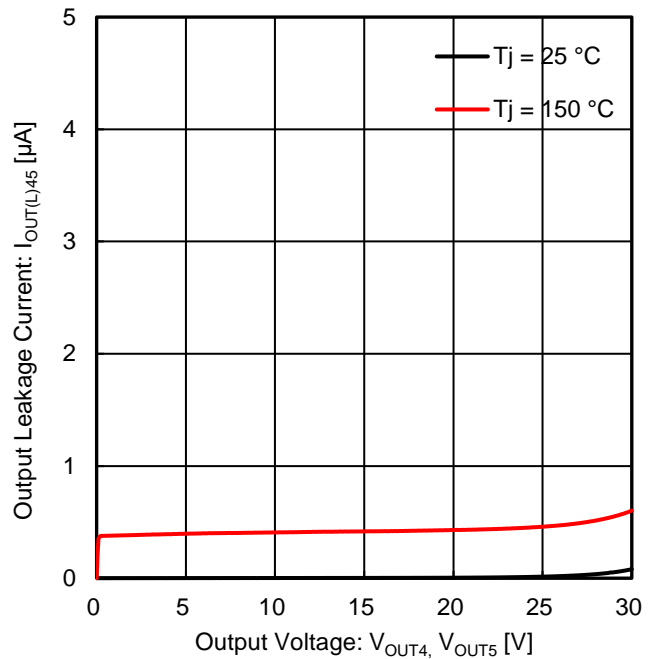


Figure 33. Output Leakage Current vs Output Voltage (OUT4, OUT5)

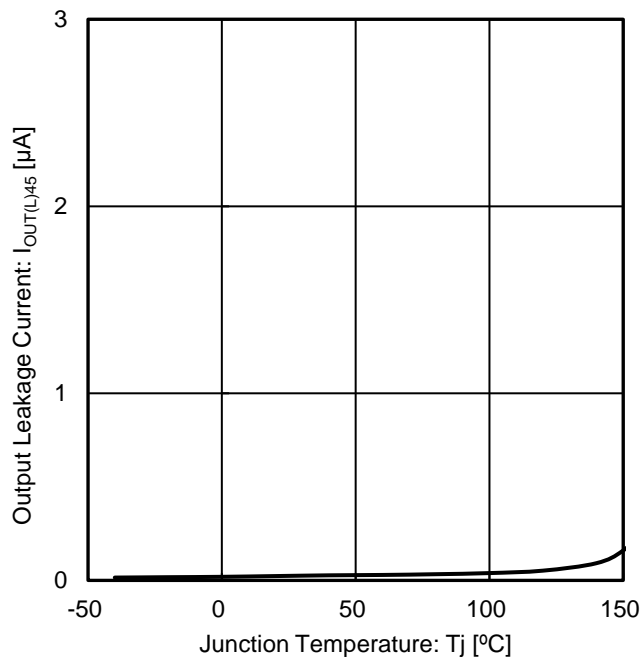


Figure 34. Output Leakage Current vs Junction Temperature (OUT4, OUT5)

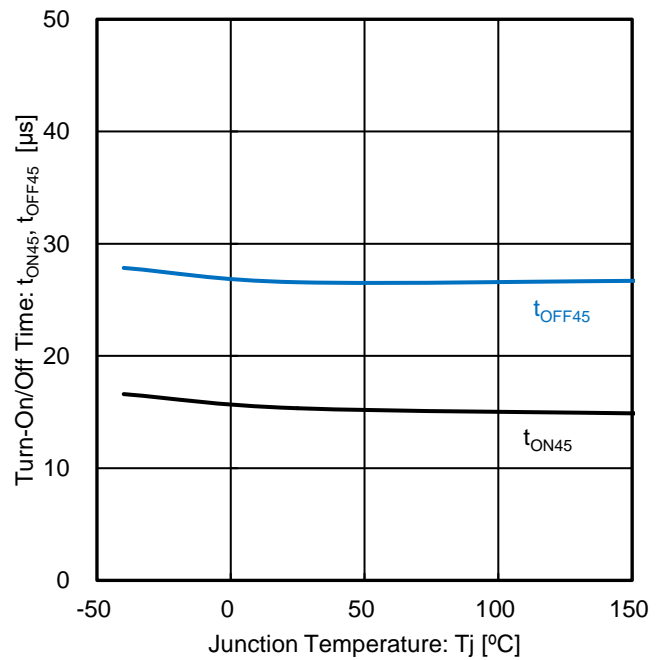


Figure 35. Turn-On Time / Turn-Off Time vs Junction Temperature (OUT4, OUT5)

Typical Performance Curves – continued

(Reference data) (Unless otherwise specified, $V_X = 12\text{ V}$, $V_S = 7\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$)

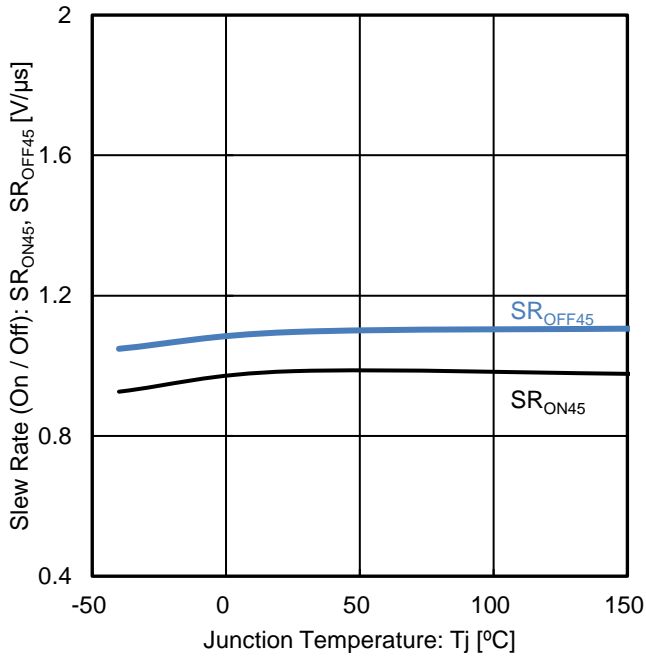


Figure 36. Slew Rate (On) / Slew Rate (Off) vs Junction Temperature (OUT4, OUT5)

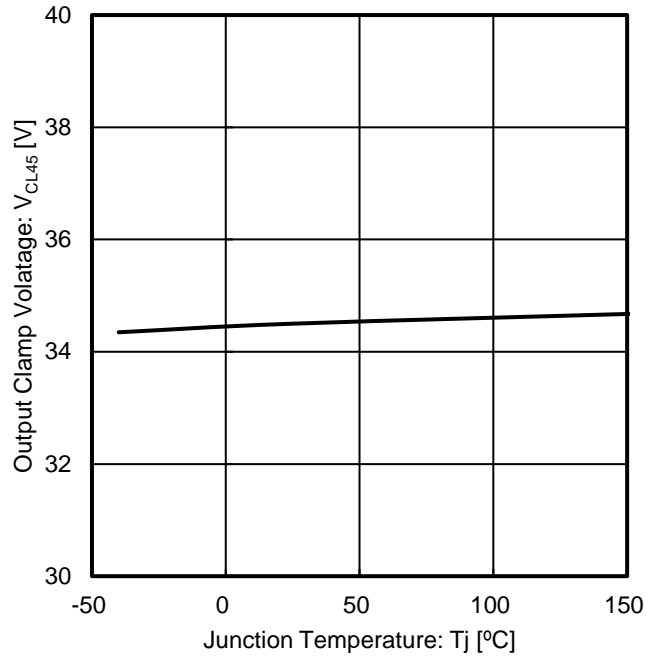


Figure 37. Output Clamp Voltage vs Junction Temperature (OUT4, OUT5)

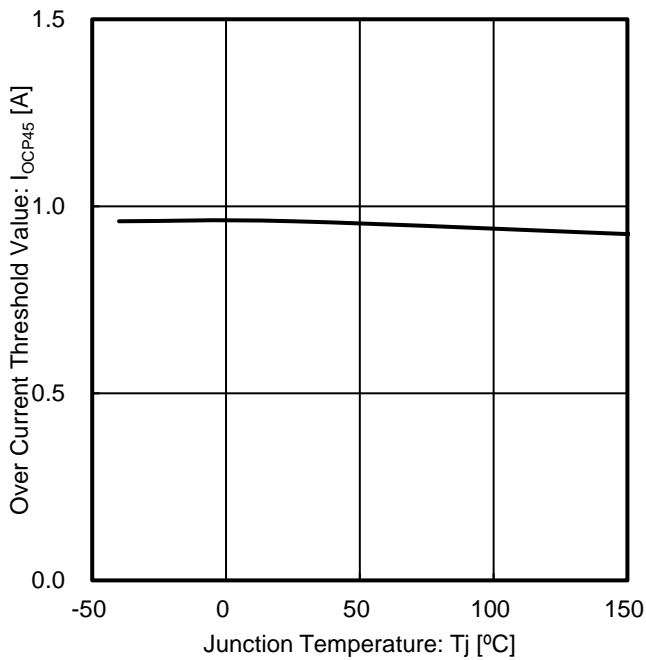


Figure 38. Over Current Threshold Value vs Junction Temperature (OUT4, OUT5)

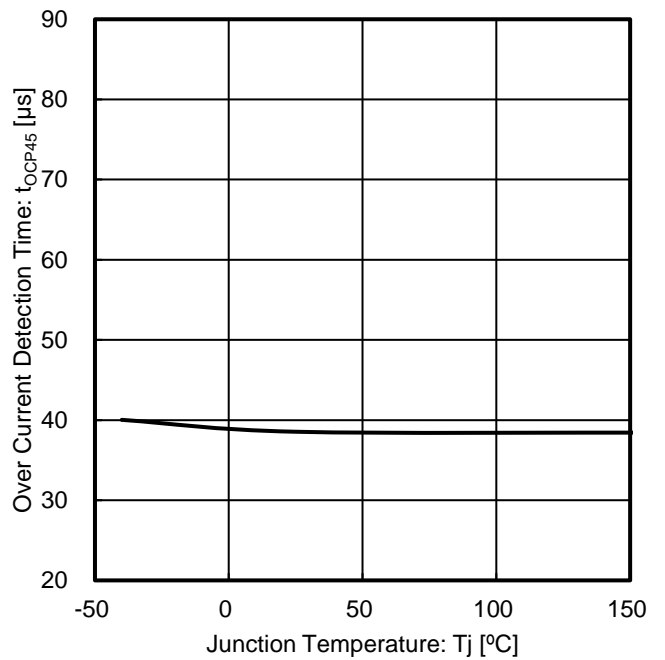


Figure 39. Over Current Detection Time vs Junction Temperature (OUT4, OUT5)

Typical Performance Curves – continued

(Reference data) (Unless otherwise specified, $V_X = 12\text{ V}$, $V_S = 7\text{ V}$, $T_J = 25\text{ }^\circ\text{C}$)

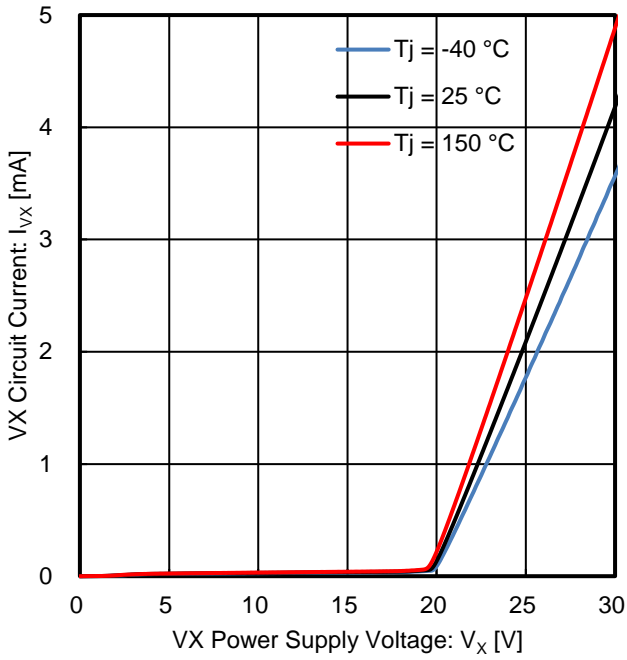


Figure 40. VX Circuit Current vs VX Power Supply Voltage

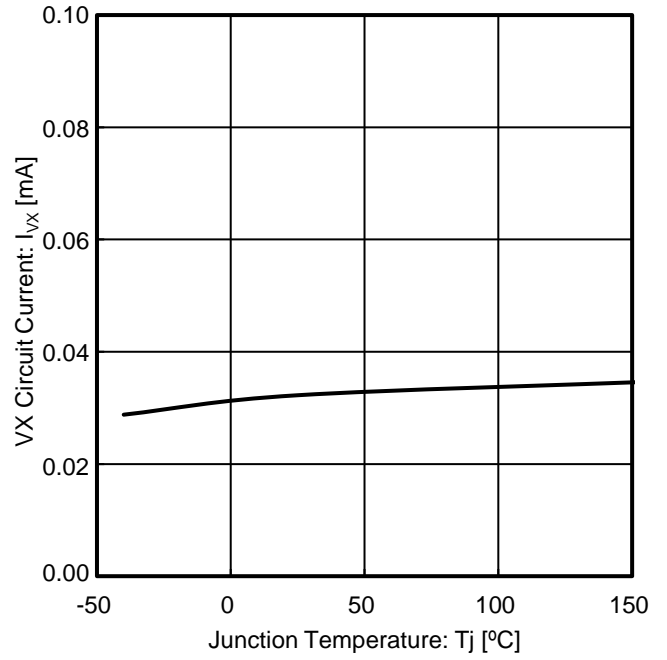


Figure 41. VX Circuit Current vs Junction Temperature

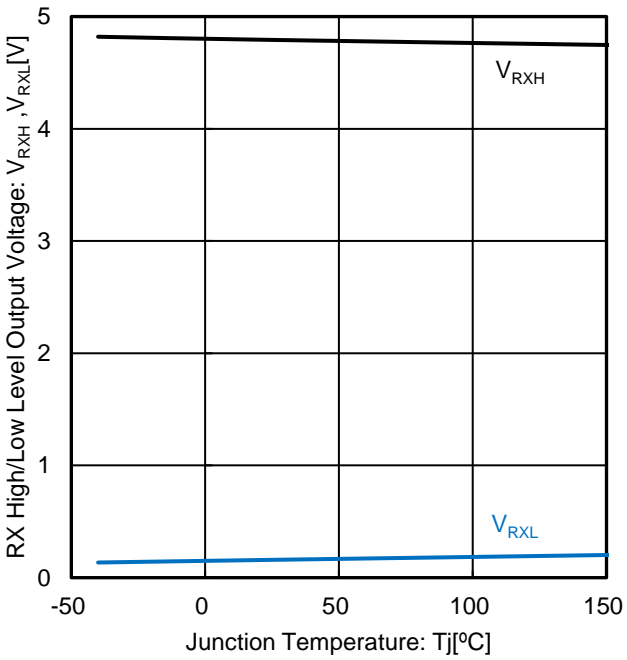


Figure 42. RX High Level Output Voltage / RX Low Level Output Voltage vs Junction Temperature

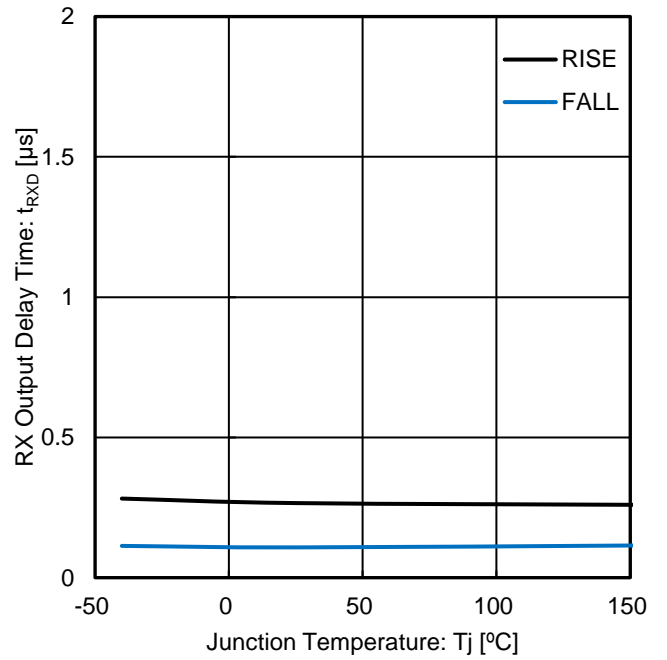


Figure 43. RX Output Delay Time vs Junction Temperature

Typical Performance Curves – continued

(Reference data) (Unless otherwise specified, $V_X = 12\text{ V}$, $V_S = 7\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$)

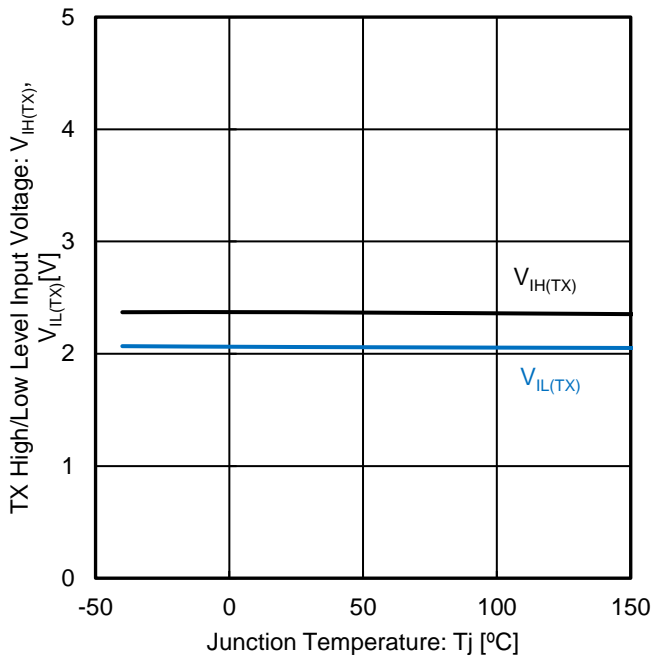


Figure 44. TX High Level Input Voltage / TX Low Level Input Voltage vs Junction Temperature

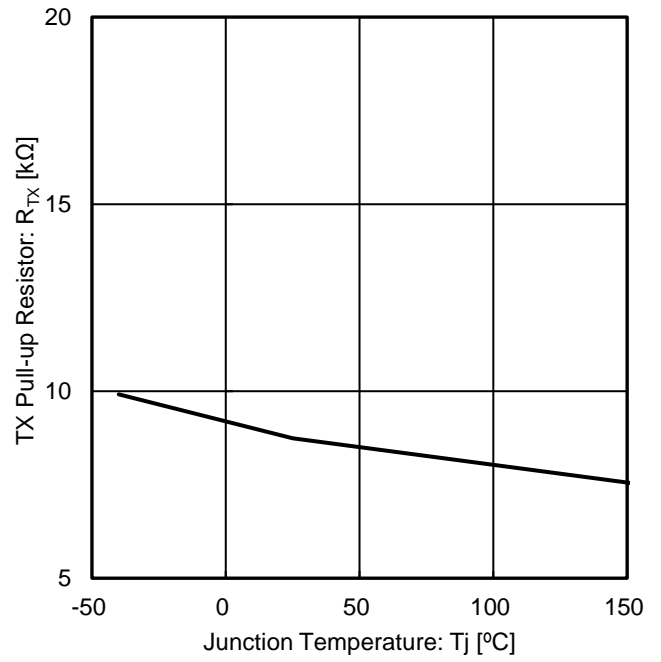


Figure 45. TX Pull-up Resistor vs Junction Temperature

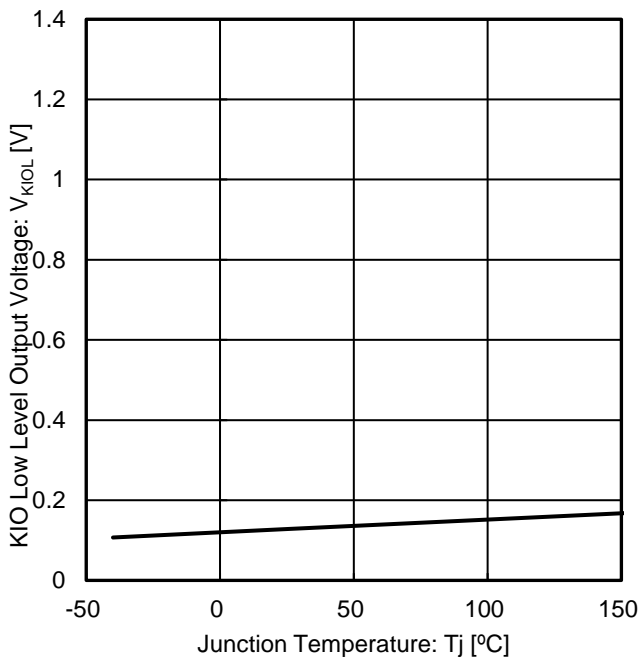


Figure 46. KIO Low Level Output Voltage vs Junction Temperature

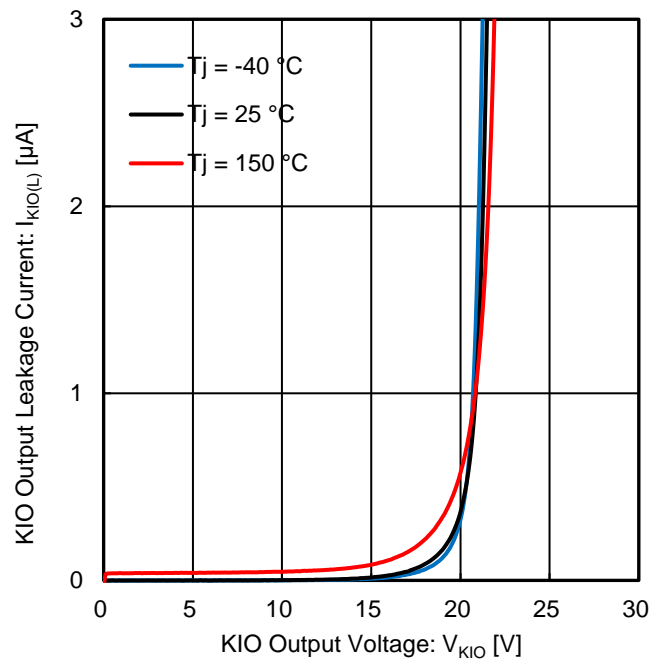


Figure 47. KIO Output Leakage Current vs KIO Output Voltage

Typical Performance Curves – continued

(Reference data) (Unless otherwise specified, $V_X = 12\text{ V}$, $V_S = 7\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$)

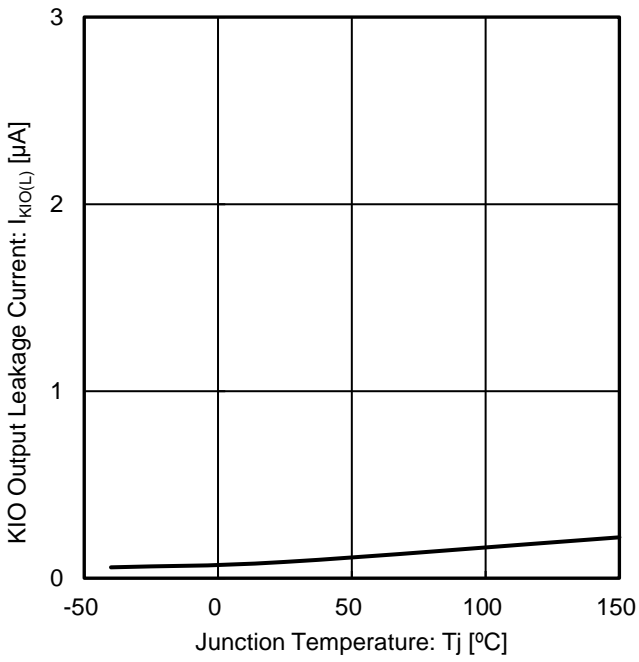


Figure 48. KIO Output Leakage Current vs Junction Temperature

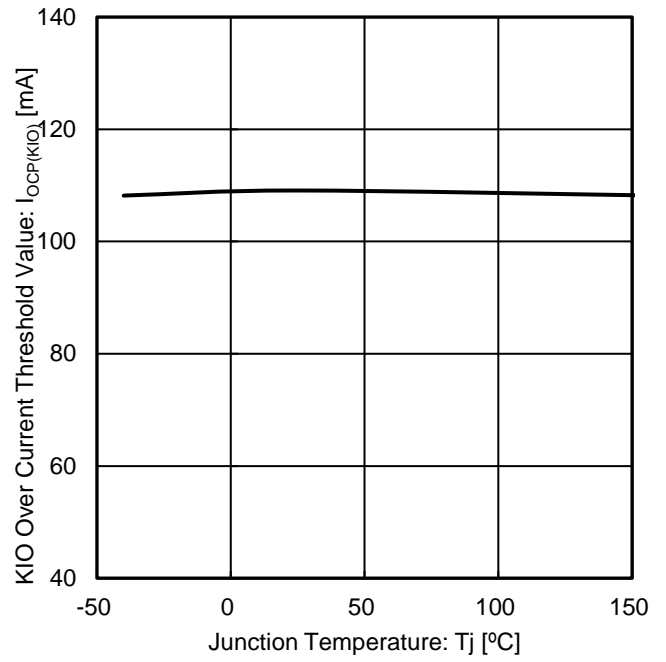


Figure 49. KIO Over Current Threshold Value vs Junction Temperature

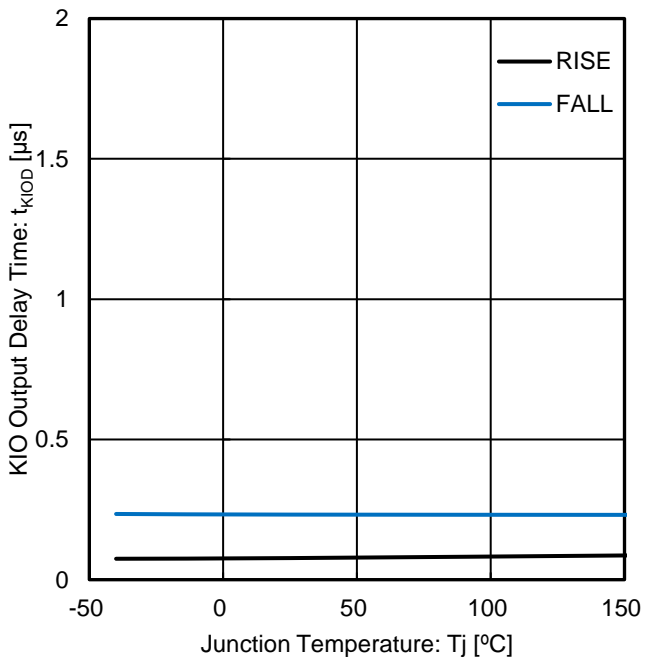


Figure 50. KIO Output Delay Time vs Junction Temperature

Measurement Circuits

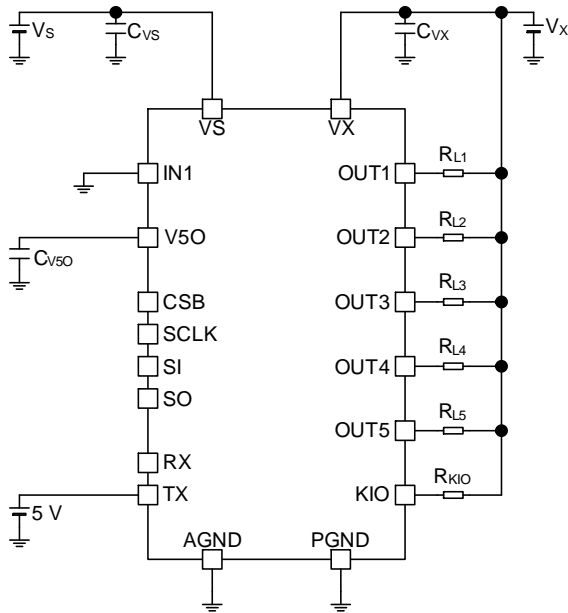


Figure 51.
VS Circuit Current
VX Circuit Current

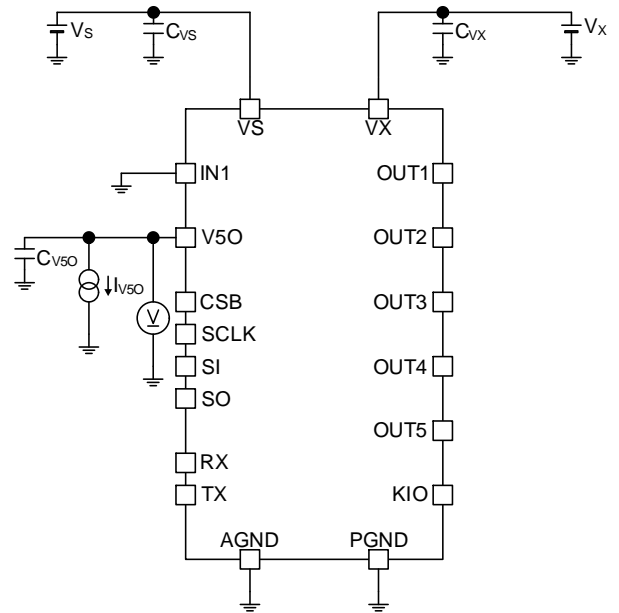


Figure 52.
V50 Output voltage
Load Regulation
Line Regulation
Low Dropout Voltage

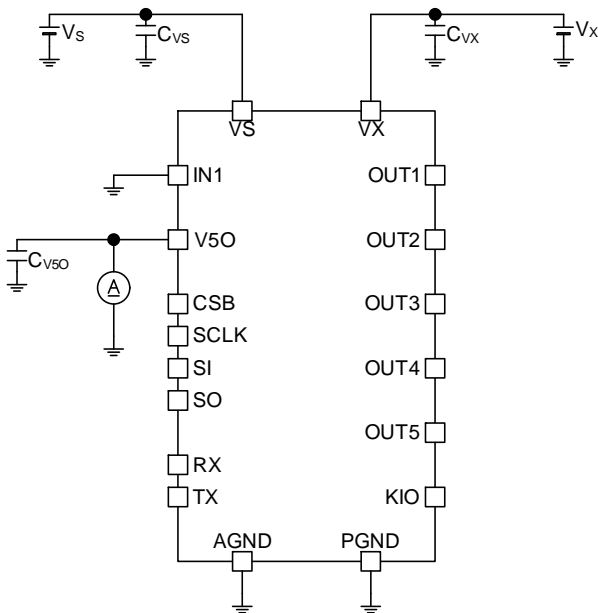


Figure 53.
V50 Over Current Threshold Value

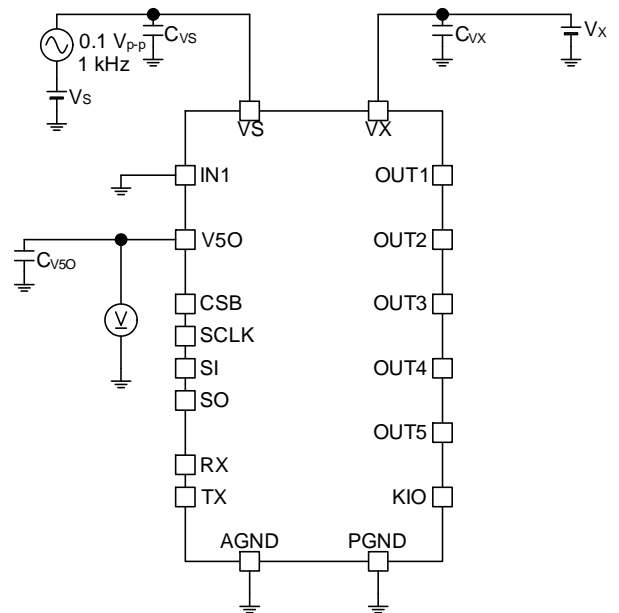


Figure 54.
Power Supply Ripple Rejection Ratio

Measurement Circuits – continued

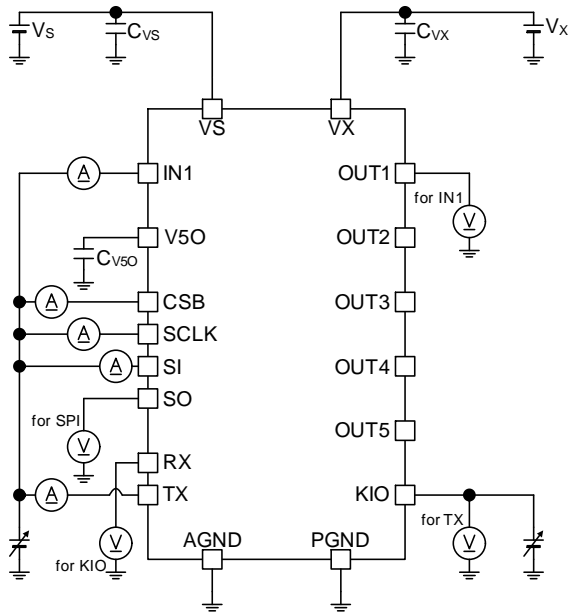


Figure 55.
 High Level Input Voltage
 Low Level Input Voltage
 Input Hysteresis Voltage
 High Level Input Current 1
 Low Level Input Current 1
 High Level Input Current 2
 Low Level Input Current 2
 TX Pull-up Resistor

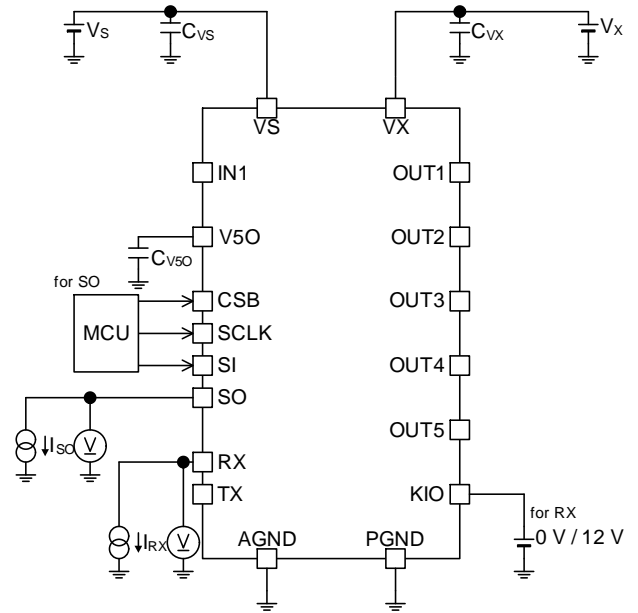


Figure 56.
 SO High Level Output Voltage
 SO Low Level Output Voltage
 RX High Level Output Voltage
 RX Low Level Output Voltage

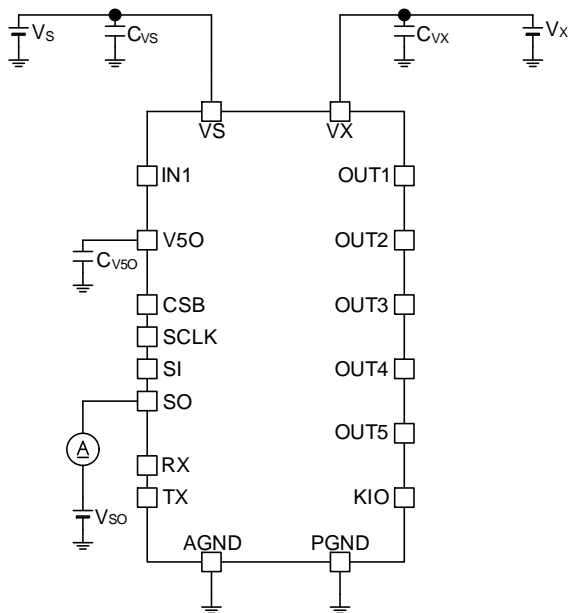


Figure 57.
 Serial Out Output Leakage Current

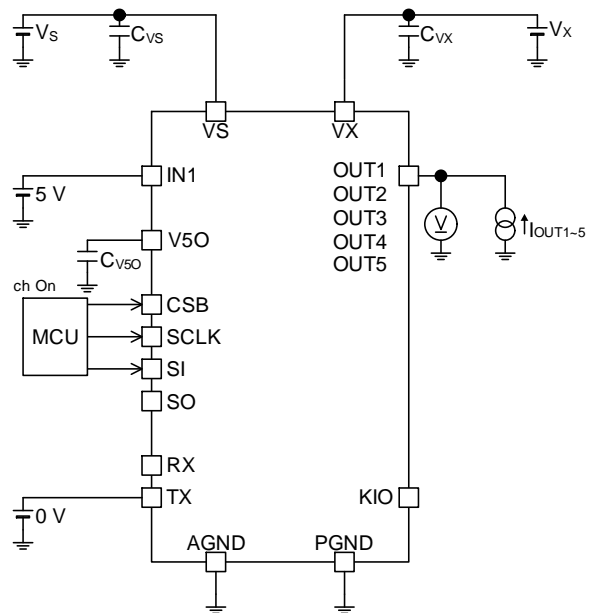


Figure 58.
 Output On Resistance

Measurement Circuits – continued

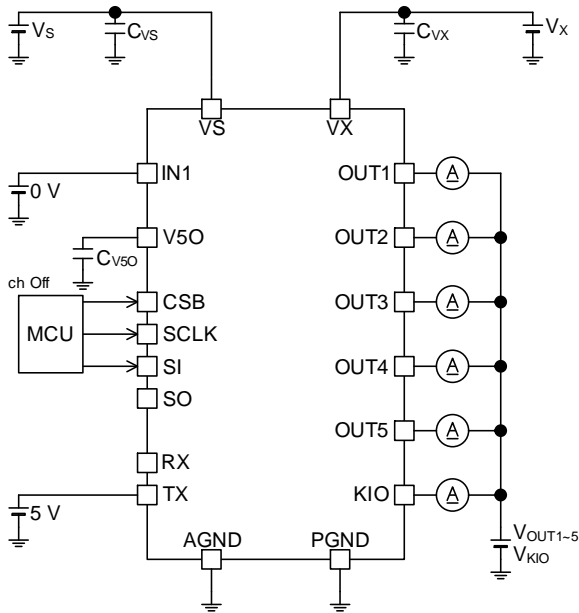


Figure 59.
Output Sink Current During OLD
Output Leakage Current
KIO Output Leakage Current

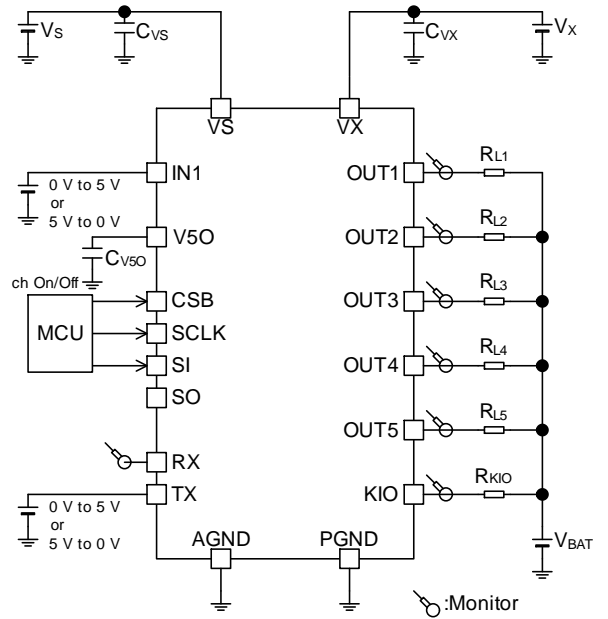


Figure 60.
Turn-On Time
Turn-Off Time
Slew Rate (On)
Slew Rate (Off)
RX Output Delay Time
KIO Output Delay Time

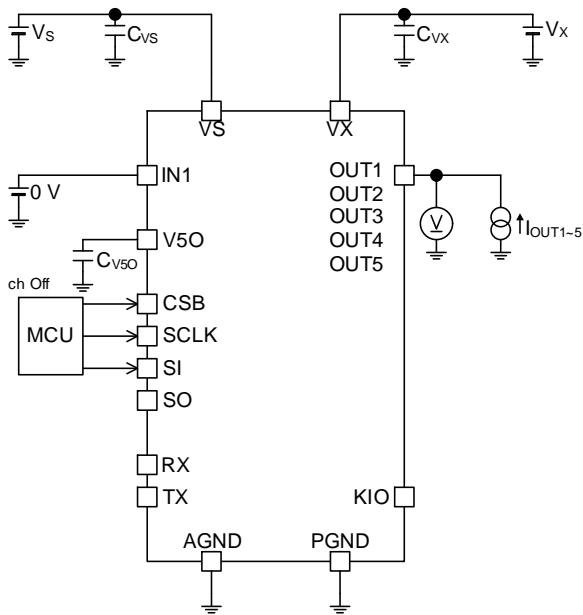


Figure 61.
Output Clamp Voltage

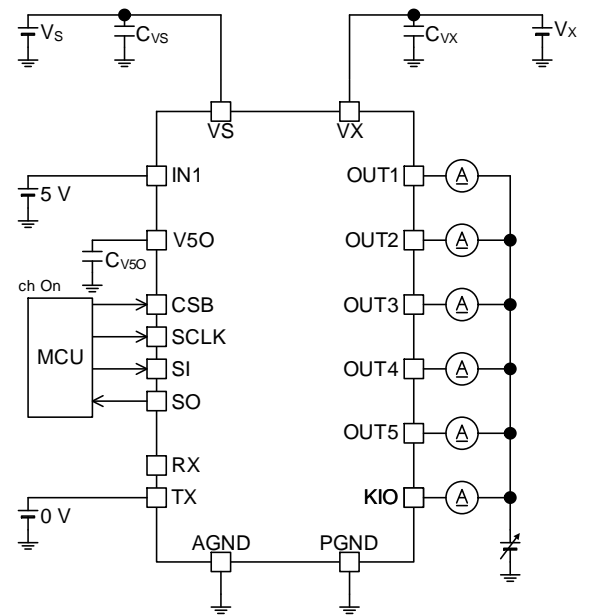


Figure 62.
Over Current Threshold Value
Over Current Detection Time
KIO Over Current Threshold Value

Measurement Circuits – continued

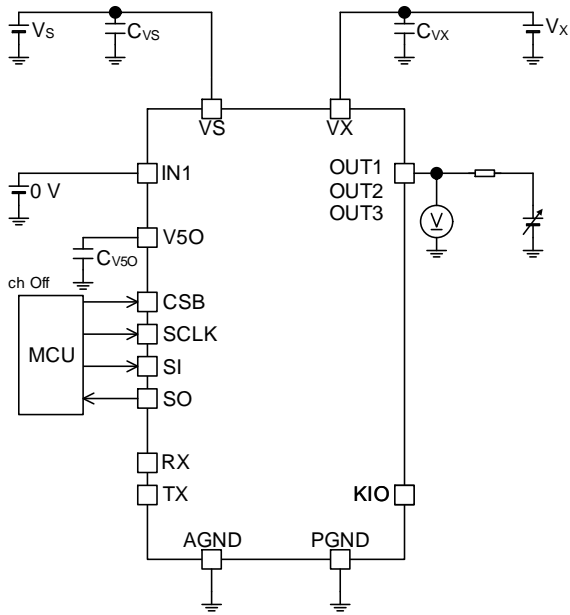


Figure 63.
Open Load Detect Voltage
Open Load Detect Release Voltage

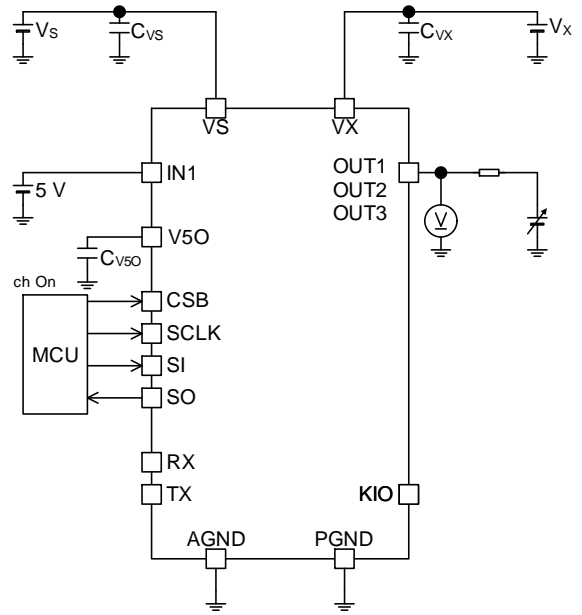


Figure 64.
Output Overhead Detect Voltage
Output Overhead Detect Release Voltage

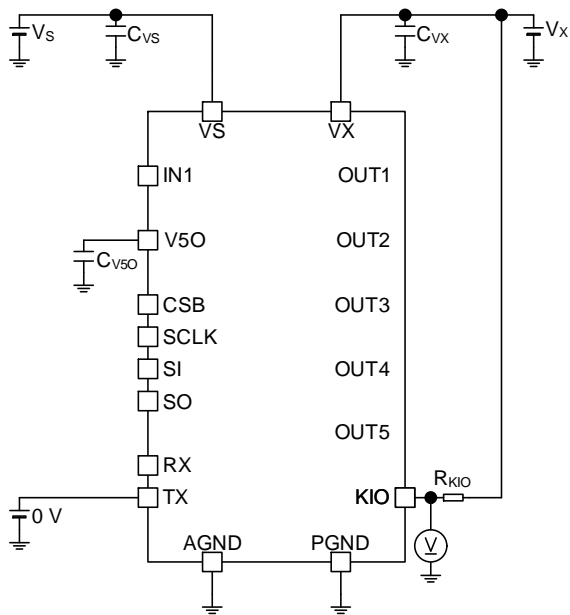
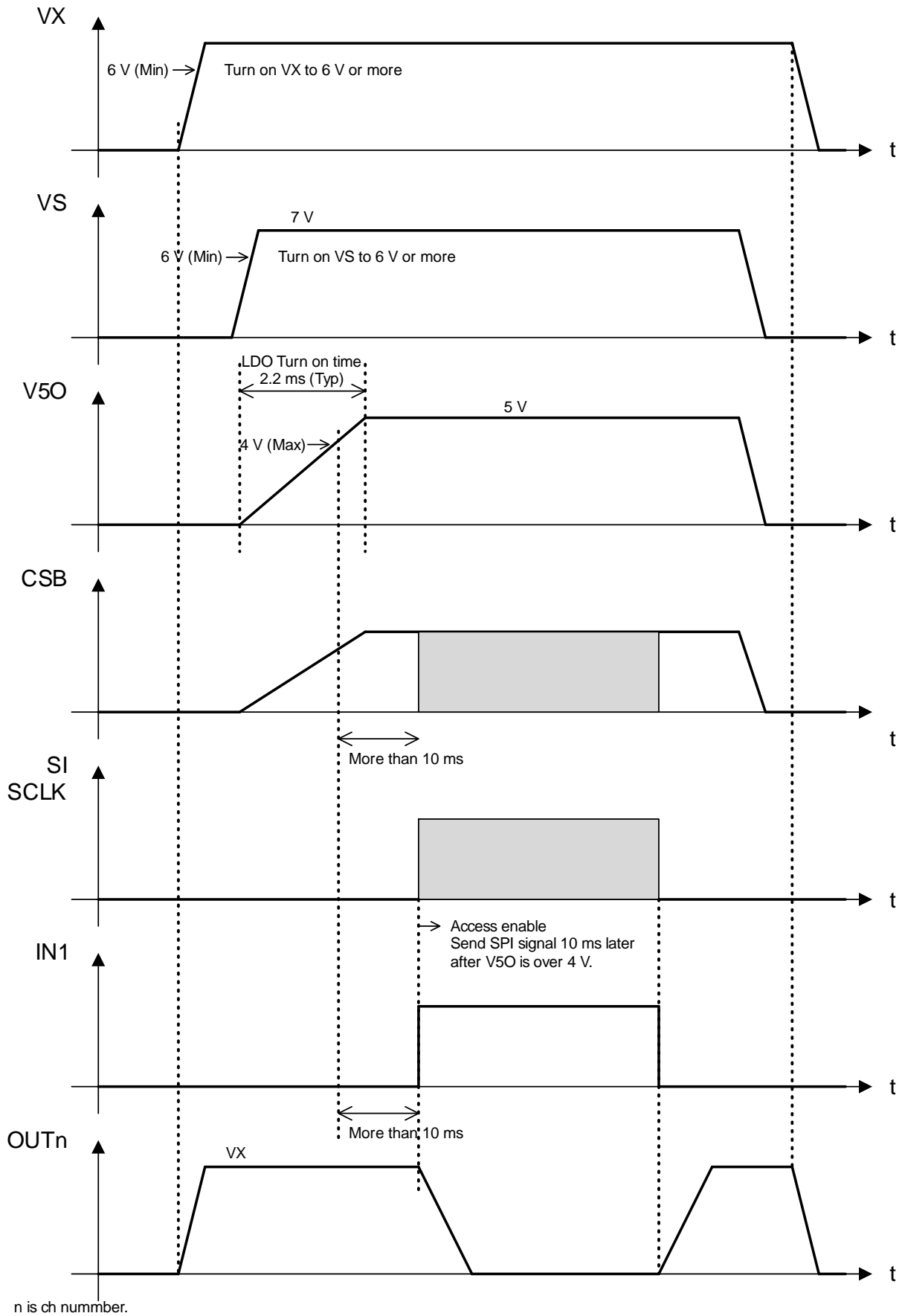
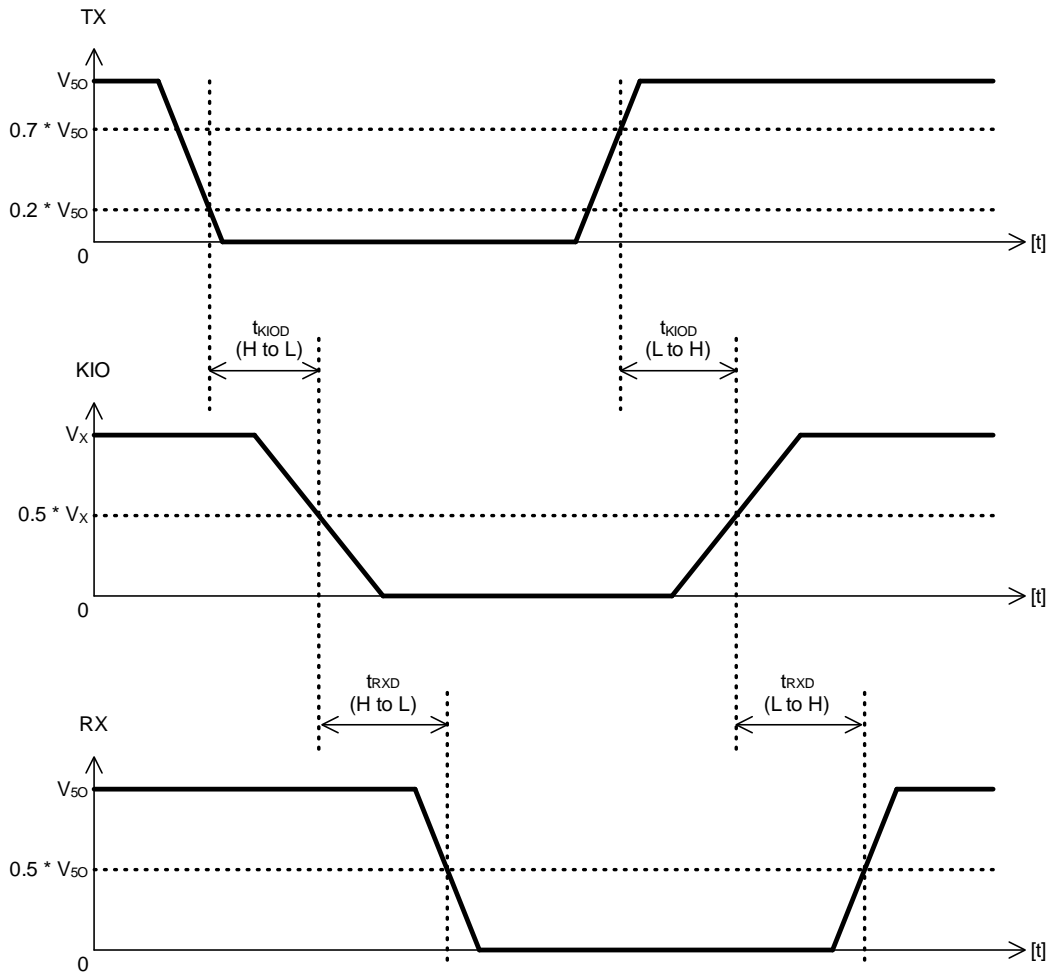


Figure 65.
KIO Low Level Output Voltage

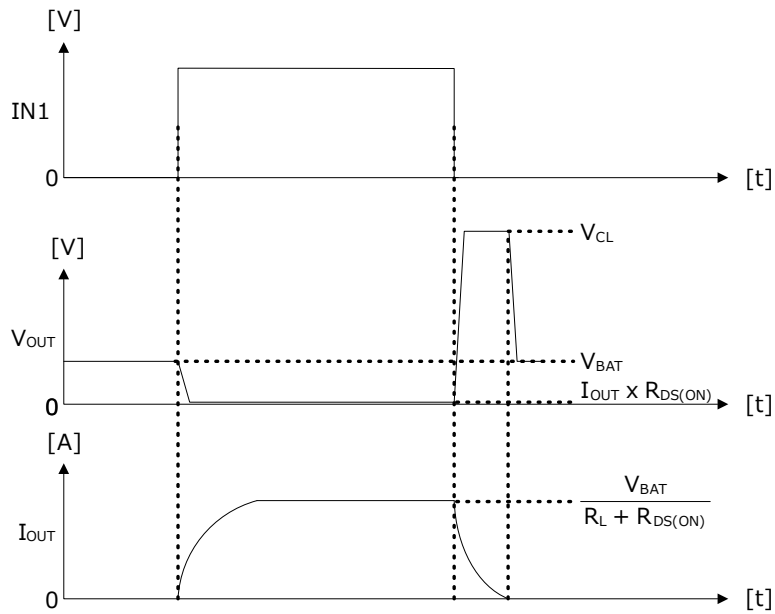
Timing Chart



K-LINE Timing Chart



Output waveform During Inductive Load Operation



SPI Specification

·SPI Overview

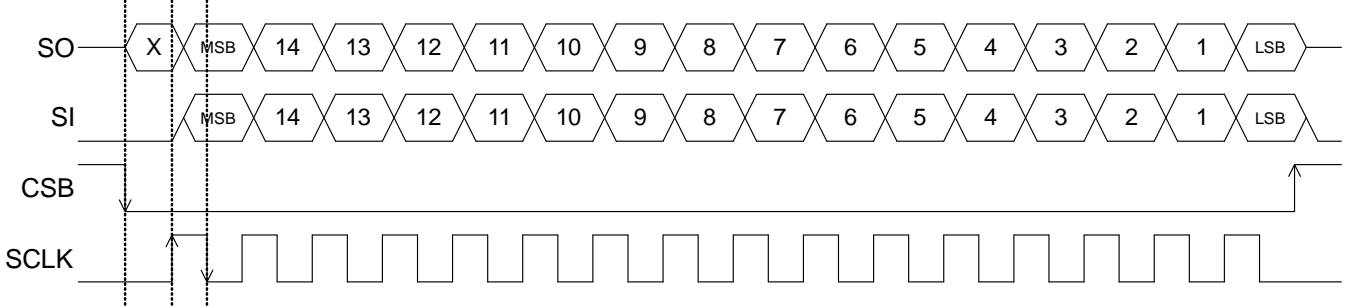
When CSB = H

The SO pin is High-Z.

When CSB = L

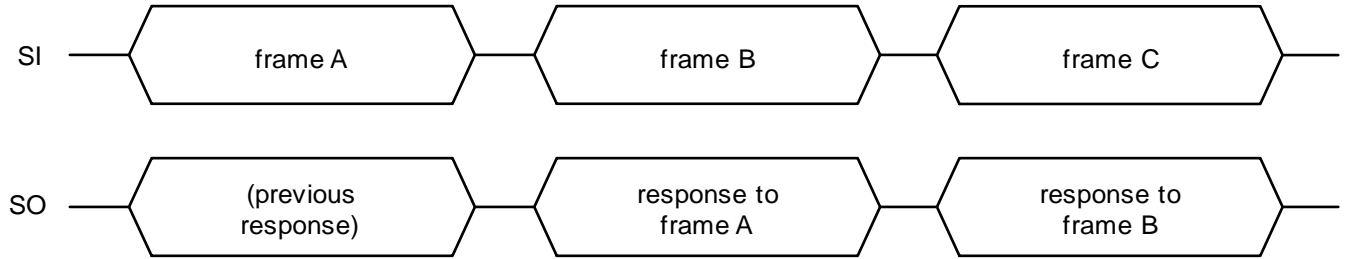
Outputs to SO at the rising edge of SCLK.

SI is loaded into the register at the falling edge of SCLK.



·SPI Protocol

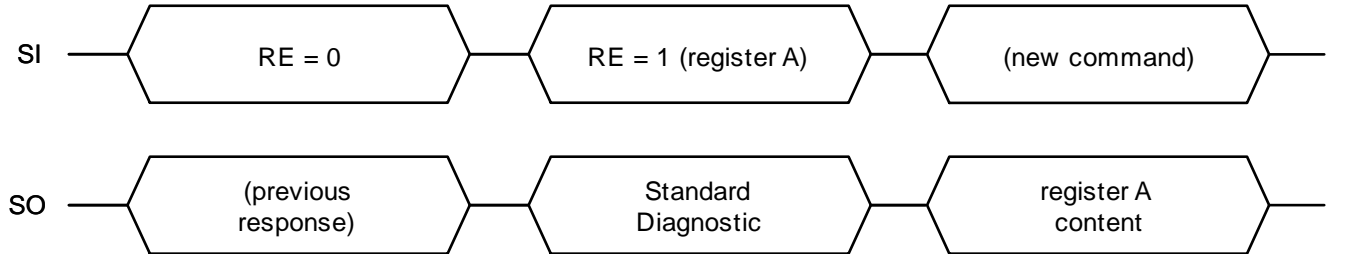
The SO response to SPI access is returned at the next SPI access as shown in the following figure.



·Response when accessing with RE = 0 and with RE = 1

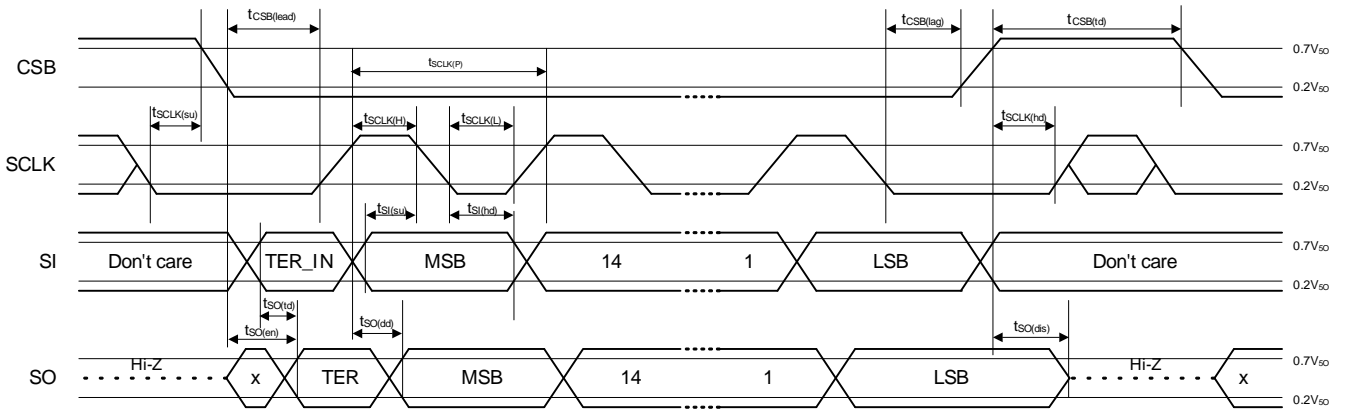
When accessing with RE = 0, respond "Standard Diagnostic".

When accessing with RE = 1, respond the value of the specified register.



SPI Specification – continued

·SPI Timing Chart



| Parameter | Symbol | Min | Typ | Max | Unit |
|--|-----------------|-----|-----|-----|------|
| SCLK Frequency | f_{SCLK} | 0 | - | 5 | MHz |
| SCLK Period | $t_{SCLK(P)}$ | 200 | - | - | ns |
| SCLK High Time | $t_{SCLK(H)}$ | 50 | - | - | ns |
| SCLK Low Time | $t_{SCLK(L)}$ | 50 | - | - | ns |
| SCLK Setup Time | $t_{SCLK(su)}$ | 50 | - | - | ns |
| SCLK Hold Time | $t_{SCLK(hd)}$ | 50 | - | - | ns |
| CSB Lead Time | $t_{CSB(lead)}$ | 250 | - | - | ns |
| CSB Lag Time | $t_{CSB(lag)}$ | 250 | - | - | ns |
| Transfer Delay Time | $t_{CSB(td)}$ | 250 | - | - | ns |
| Data Setup Time | $t_{SI(su)}$ | 20 | - | - | ns |
| Data Hold Time | $t_{SI(hd)}$ | 20 | - | - | ns |
| SPI Output Enable Time ^(Note 1) | $t_{SO(en)}$ | - | - | 200 | ns |
| SPI Output Disable Time ^(Note 1) | $t_{SO(dis)}$ | - | - | 250 | ns |
| SPI Output Data Delay Time ^{(Note 1)(Note 2)} | $t_{SO(dd)}$ | - | - | 100 | ns |
| ERR Output Through Delay Time ^(Note 1) | $t_{SO(td)}$ | - | - | 200 | ns |

(Note 1) Not 100 % tested.

(Note 2) SO pin capacitance = 20 pF

SPI Specification – continued

·SI Data Structure

| Bit[15] | Bit[14] | Bit[13] | Bit[12] | Bit[11] | Bit[10] | Bit[9] | Bit[8] | Bit[7] | Bit[6] | Bit[5] | Bit[4] | Bit[3] | Bit[2] | Bit[1] | Bit[0] |
|---------|---------|---------|---------|---------|---------|--------|--------|--------|--------|--------|--------|--------|--------|--------|--------|
| RE | WE | Address | | | | | TEST | Data | | | | | | | |

RE

- 0: The SO pin outputs "Standard Diagnostic" at the next SPI access.
- 1: The SO pin outputs the register value specified by Address at the next SPI access.

WE

- 0: Not Write.
- 1: Write.

TEST

Be sure to set 0.

Data

When WE = 1, various settings are enabled by writing '0' or '1' to Data.
For details, refer to "Register Map".

·"Standard Diagnostic" (when RE = 0 setting in the previous SPI access)

Initial Value 0x4000

| Bit[15] | Bit[14] | Bit[13] | Bit[12] | Bit[11] | Bit[10] | Bit[9] | Bit[8] | Bit[7] | Bit[6] | Bit[5] | Bit[4] | Bit[3] | Bit[2] | Bit[1] | Bit[0] |
|---------|---------|---------|---------|---------|---------|--------|--------------|--------|--------|--------|--------|--------|--------|--------|--------|
| 0 | INIT | 0 | 0 | 0 | TER | 0 | TSD KLINE | OLD3 | OLD2 | OLD1 | ERR5 | ERR4 | ERR3 | ERR2 | ERR1 |

INIT

- 0: Normal (after power on, from the second time SPI access).
- 1: After power on, first time SPI access.

TER

- 0: Normal
- 1: SPI communication error
When High pulse input of SCLK is other than (16 times + 8 x m, m is an integer 0 or above) in the low level section of CSB, a communication error is judged.

TSDKLINE

- 0: Normal
- 1: Thermal shutdown of K-LINE section
Once detected, it latches." Standard Diagnostic" is cleared by read access.

DIAG_OLDn (n shows ch number)

- 0: Normal
- 1: Open load detection of OUT1, OUT2, OUT3
Once detected, it latches." Standard Diagnostic" is cleared by read access.

ERRn (n shows ch number)

- 0: Normal
- 1: Over current protection, thermal shutdown, or output overhead detection (OUT1, OUT2, OUT3 only) for OUTn
(Logical OR of DIAG_OCPn, DIAG_TSDn, and DIAG_OFDn)

·SO Output Data Structure (when RE = 1 setting in the previous SPI access)

| Bit[15] | Bit[14] | Bit[13] | Bit[12] | Bit[11] | Bit[10] | Bit[9] | Bit[8] | Bit[7] | Bit[6] | Bit[5] | Bit[4] | Bit[3] | Bit[2] | Bit[1] | Bit[0] |
|---------|---------|---------|---------|---------|---------|--------|--------------------|--------|--------|--------|--------|--------|--------|--------|--------|
| 1 | WE | Address | | | | | ERR _{ALL} | Data | | | | | | | |

WE, Address

Outputs WE and Address values that were set during the previous SPI access.

ERR_{ALL}

Outputs 1 when either open load detection, output overhead detection, over current protection or thermal shutdown is detected on at least one channel.
(Logical OR of DIAG_OLDn, DIAG_OFDn, DIAG_OCPn, DIAG_TSDn and DIAG_TSD_KLINE for all channels)

Data

Outputs the register value of Address that were set during the previous SPI access.

Register Map

| Register Name | Register Access | Address | TEST | Data | | | | | | | | Initial |
|---------------|-----------------|-----------|--------|-----------|-----------|-----------|-----------|----------|-----------|-----------|------------|---------|
| | | Bit[13:9] | Bit[8] | Bit[7] | Bit[6] | Bit[5] | Bit[4] | Bit[3] | Bit[2] | Bit[1] | Bit[0] | |
| OUTCTRL | R/W | 0x00 | 0 | 0 | 0 | 0 | OUTCTRL5 | OUTCTRL4 | OUTCTRL3 | OUTCTRL2 | 0 | 0x00 |
| STATUS_IN | RO | 0x06 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | STATUS_IN1 | 0x00 |
| DIAG_OUT32 | RO | 0x0A | 0 | 0 | DIAG_OFD3 | DIAG_OCP3 | DIAG_TSD3 | 0 | DIAG_OFD2 | DIAG_OCP2 | DIAG_TSD2 | 0x00 |
| DIAG_OUT541 | RO | 0x0B | 0 | DIAG_OCP5 | DIAG_TSD5 | DIAG_OCP4 | DIAG_TSD4 | 0 | DIAG_OFD1 | DIAG_OCP1 | DIAG_TSD1 | 0x00 |
| HWCR | WO | 0x0C | 0 | 0 | RST | 0 | 0 | 0 | 0 | 0 | 0 | 0x00 |
| T_TESTMODE | WO | 0x1E | 1 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | TESTMODE | 0x00 |

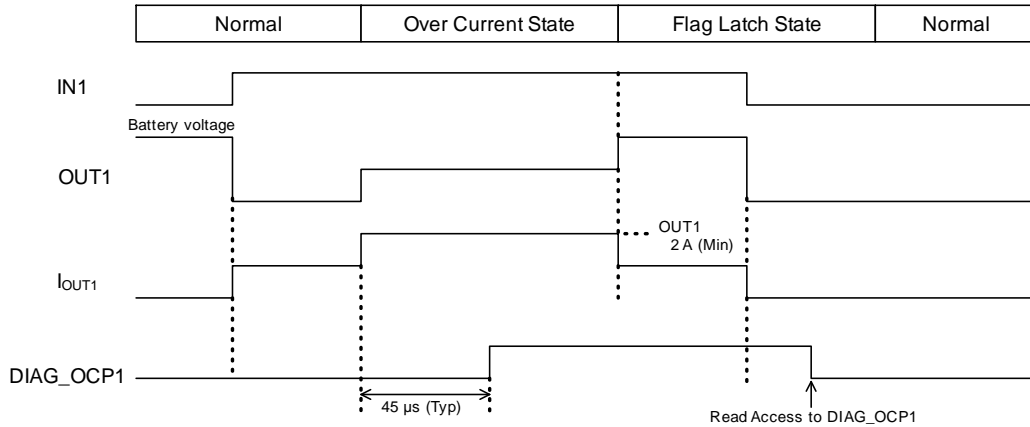
| Register Name | Register Access | Address | Explanation of Data |
|---------------------------|-----------------|----------------|---|
| OUTCTRL | Read / Write | 0x00h | OUTCTRLn bit (n represents the channel number) '0': OUTn off setting '1': OUTn on setting |
| STATUS_IN | Read Only | 0x06h | STATUS_IN1 bit '0': IN1 L input, OUT1 Off Setting '1': IN1 H input, OUT1 On Setting |
| DIAG_OUT32 DIAG_OUT541 | Read Only | 0x0Ah 0x0Bh | Reads the error flags of OUT1 to OUT5. DIAG_OFDn bit '0': Normal '1': Output overhead detection Once detected, it latches. Cleared by read access to DIAG_OFDn. DIAG_OCPn bit '0': Normal '1': Over current protection detection It latches, if over current protection is detected at the same time as thermal shutdown or if continue detecting over current protection for a certain period of time. Cleared by read access to DIAG_OCPn. If over current protection is detected on OUT2 to OUT5, the OUTCTRLn bit of the corresponding channel is cleared to '0' and the output is turned off. After clearing DIAG_OCPn, OUTn is turned on by setting OUTCTRLn to '1' again. DIAG_TSDn bit '0': Normal '1': Thermal shutdown detection Once detected, it latches. Cleared by read access to DIAG_TSDn. |
| HWCR | Write Only | 0x0Ch | RST '0': Normal '1': Hardware reset (auto clear) |
| T_TESTMODE | Write Only | 0x1Eh | TESTMODE '0': Normal '1': Test Mode If IN pin is 5.6 V (Min) or more and "1" is written to this register, IC enters test mode. For this reason, do not access to this register. |

Protection Function

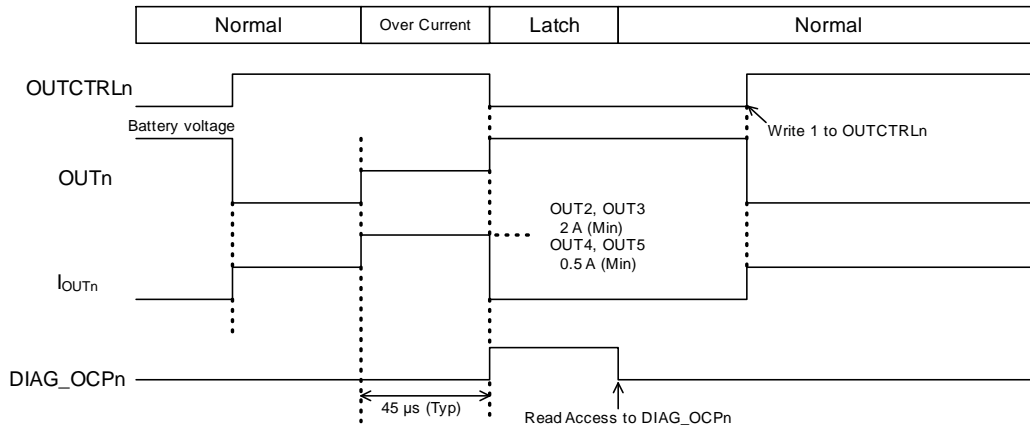
| Protection Function | | Detection and Release Conditions | | | Output Behavior | |
|---------------------|--|----------------------------------|---|--|--|---|
| Low Side Switch | Over Current Protection | Detection Conditions | OUT1 | 2 A (Min) | Current limitation | |
| | | | OUT2 OUT3 | 2 A (Min) | Output latch after 45 μ s (Typ) of current-limit state has elapsed | |
| | | | OUT4 OUT5 | 0.5 A (Min) | Output latch after 45 μ s (Typ) of current-limit state has elapsed | |
| | | Release Conditions | OUT1 | 2 A (Min) or less (automatic recovery) | Normal operation | |
| | | | OUT2 OUT3 | Write '1' to OUTCTRL2 or OUTCTRL3 after read access to DIAG_OUT32 | Output latch is released | |
| | | | OUT4 OUT5 | Write '1' to OUTCTRL4 or OUTCTRL5 after read access to DIAG_OUT541 | Output latch is released | |
| | Thermal Shutdown | Detection Condition | $T_j \geq 150 \text{ }^\circ\text{C}$ (Min) | | Output stop | |
| | | Release Condition | $T_j \leq 125 \text{ }^\circ\text{C}$ (Min) | | Normal operation | |
| | Open Load Detection (Only OUT1, OUT2 and OUT3 are supported) | Detection Condition | Output off state and Output voltage 2.0 V (Typ) or less | | Normal operation | |
| | | Release Condition | Output off state and Output voltage 2.5 V (Typ) or more | | Normal operation | |
| | Output Overhead Detection (Only OUT1, OUT2 and OUT3 are supported) | Detection Condition | Output on and Output voltage 2.5 V (Typ) or more | | Normal operation | |
| | | Release Condition | Output on and Output voltage 2.0 V (Typ) or less | | Normal operation | |
| | LDO | Over Current Protection | Detection Condition | $I_{V50} \geq 250 \text{ mA}$ (Min) | | - |
| | | | Release Condition | $I_{V50} < 250 \text{ mA}$ (Min) | | - |
| Thermal Shutdown | | Detection Condition | $T_j \geq 150 \text{ }^\circ\text{C}$ (Min) | | LDO output stopped | |
| | | Release Condition | $T_j \leq 125 \text{ }^\circ\text{C}$ (Min) | | Normal operation | |
| Power-on Reset | | Detection Condition | $V_{50} \leq 3.0 \text{ V}$ (Min) | | Low side output stopped KIO output stopped | |
| | | Release Condition | $V_{50} \geq 4.0 \text{ V}$ (Min) | | Normal operation | |
| K-LINE | KIO Over Current Protection | Detection Condition | Output current 40 mA (Min) | | Current limitation | |
| | | Release Condition | Output current 40 mA (Min) or less | | Normal operation | |
| | Thermal Shutdown | Detection Condition | $T_j \geq 150 \text{ }^\circ\text{C}$ (Min) | | KIO output stopped | |
| | | Release Condition | $T_j \leq 125 \text{ }^\circ\text{C}$ (Min) | | Normal operation | |

Over Current Protection

If a current exceeding the over current detection value flows to the low side output, over current protection is applied and an error flag (DIAG_OCPn) is output.
 For OUT1, the current flowing to the output is limited when over current protection is applied.

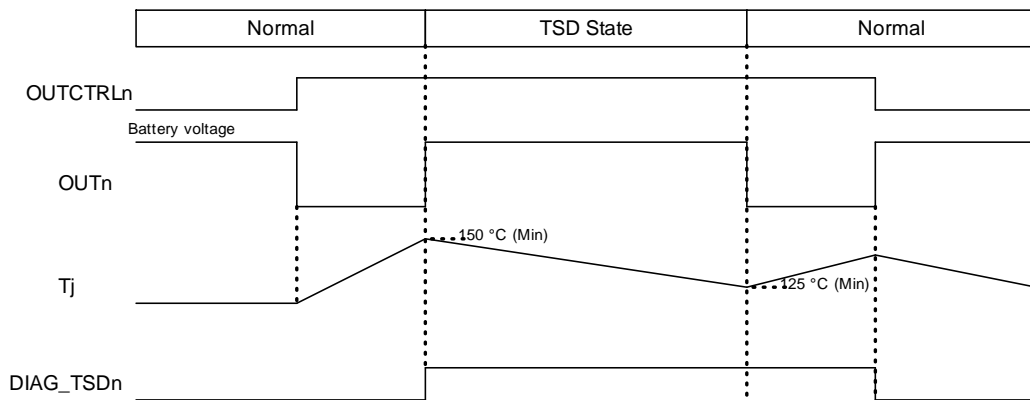


For OUT2 to OUT5, the output is turned off when over current protection is applied. In this case, OUTCTRLn is set to '0'; read access to DIAG_OCPn clears the error flag and setting OUTCTRLn to '1' turns on the output.

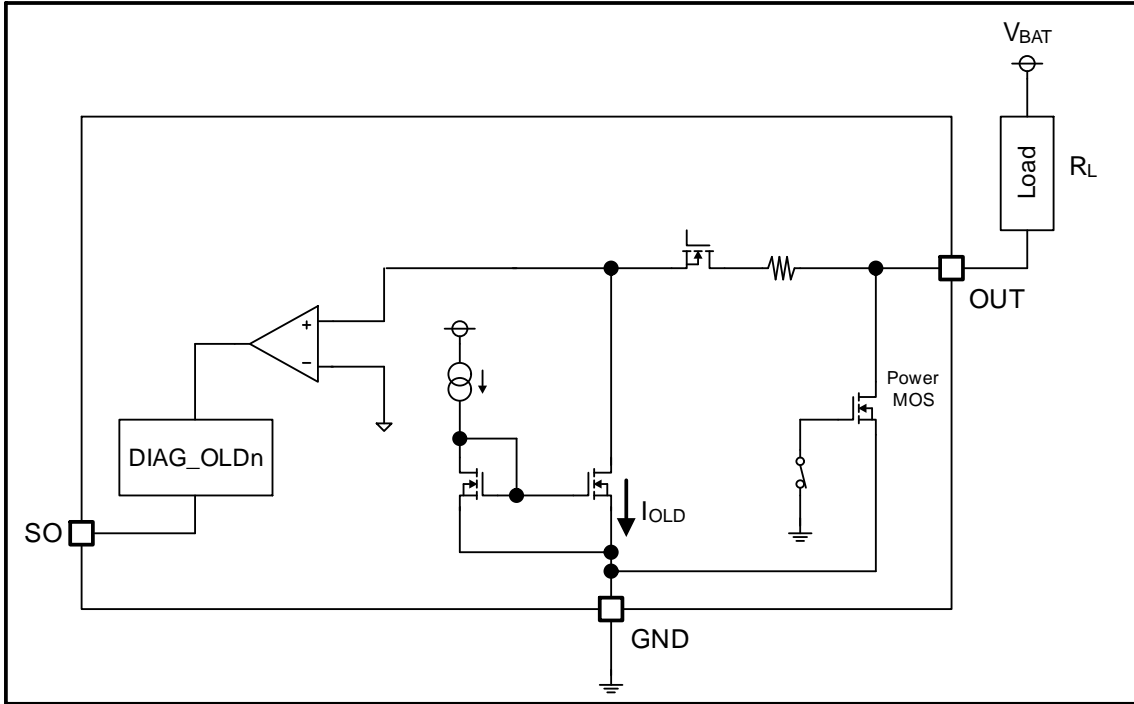


Thermal Shutdown

Turns off the low side output, LDO output, and KIO output when Tj rises 150 °C (Min) or above. Turns back on when Tj falls 125 °C (Min) or below.



Open Load Detection (OLD)



OUT1, OUT2, and OUT3 have an open load detection (OLD) function: output inflow current I_{OLD} is applied to OUT, and as load R_L increases, output voltage V_{OUT} decreases, and when it falls below $V_{OLD(ON)}$, an open load detection state occurs and an error flag is output.

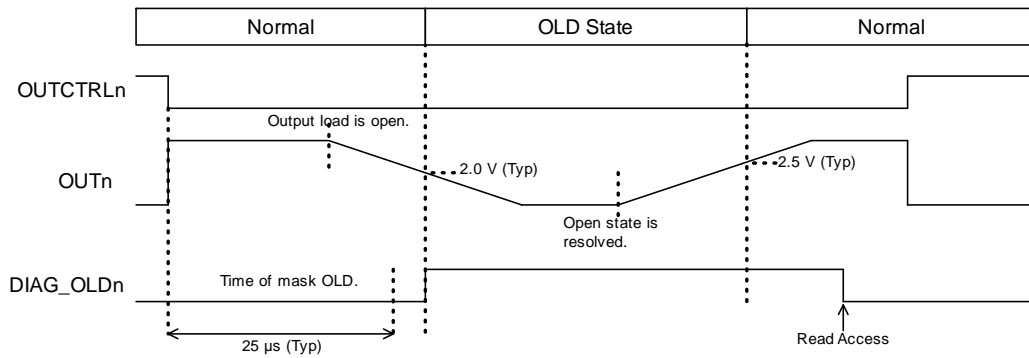
The value of R_L that detects OLD is obtained from the following formula.

$$R_L \geq \frac{V_{BAT} - V_{OLD(ON)}}{I_{OLD}}$$

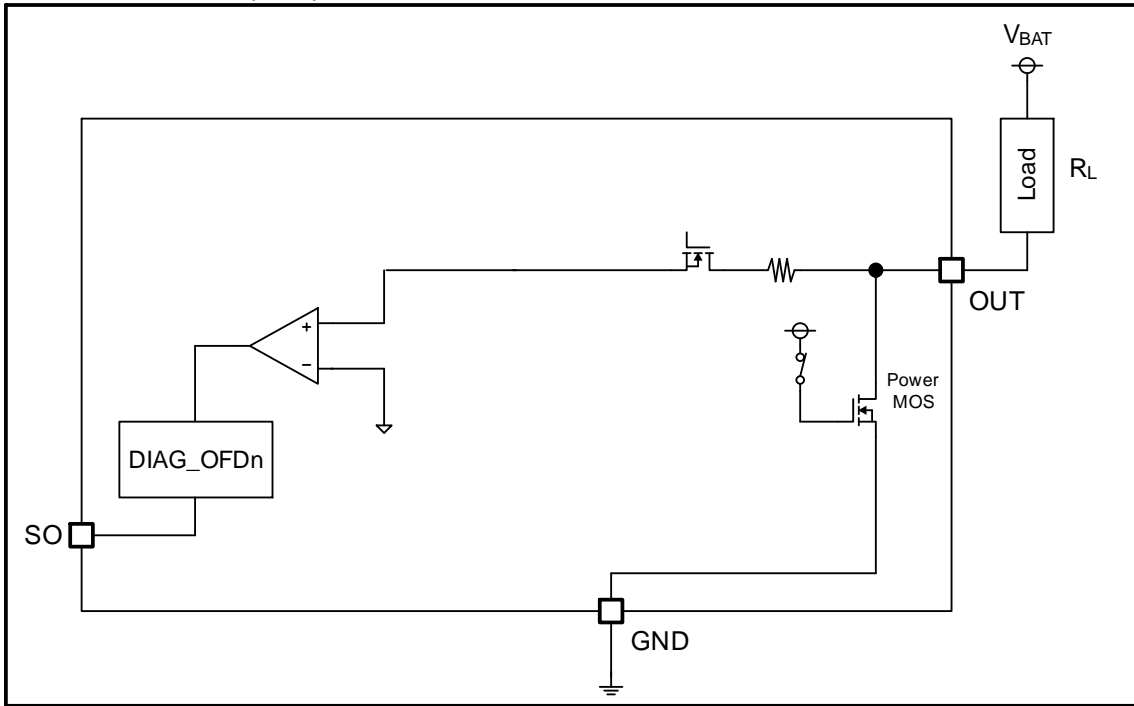
V_{BAT} : Battery voltage

$V_{OLD(ON)}$: Open load detection voltage 3.1 V (Max)

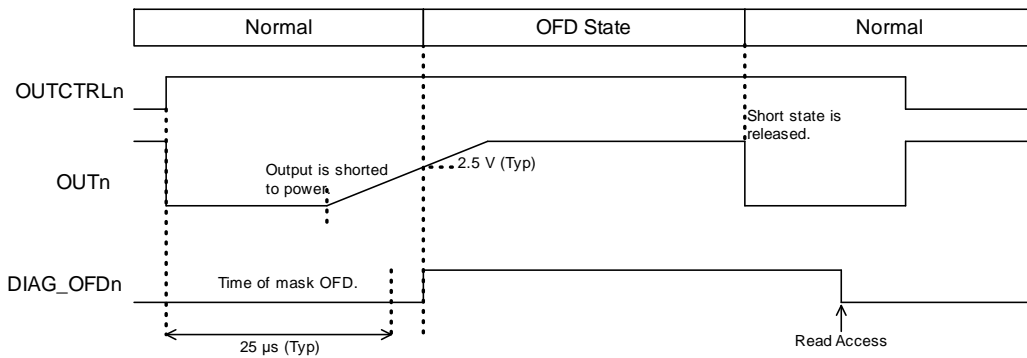
I_{OLD} : Output inflow current during open detection operation 90 μ A (Max)



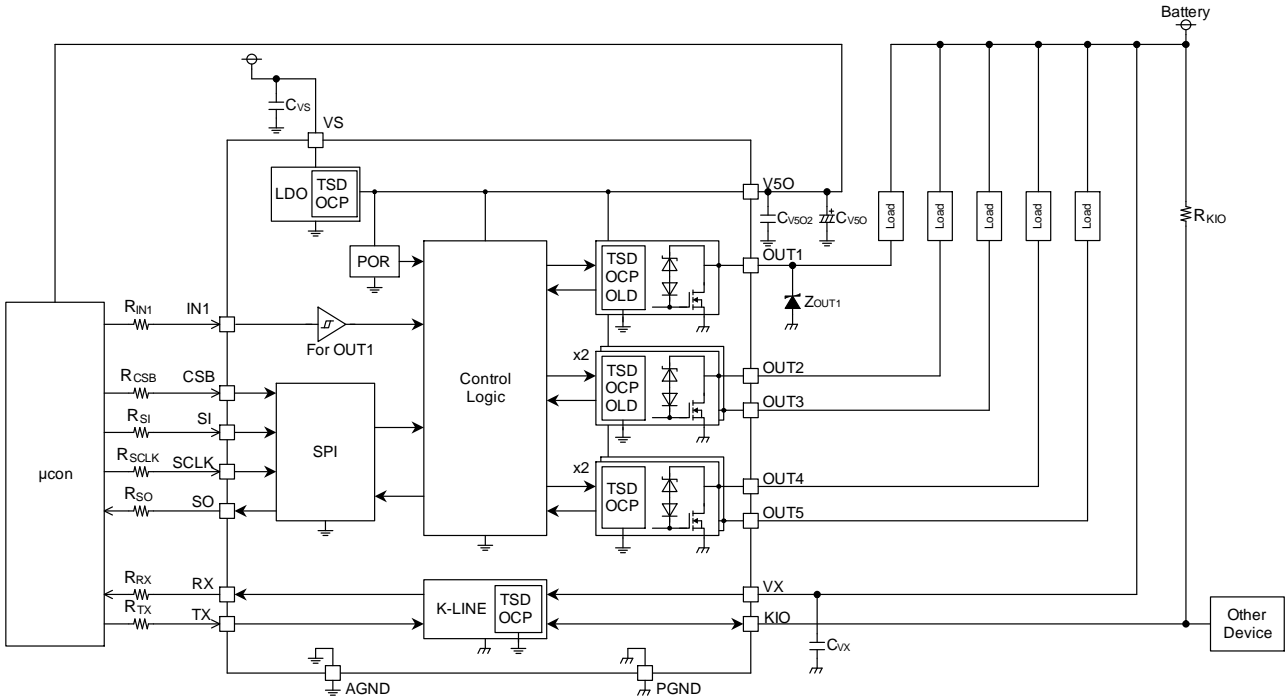
Output Overhead Detection (OFD)



OUT1, OUT2, and OUT3 have an output overhead detection (OFD) function. When the output transistor is on, if the output voltage of OUT1 to OUT3 exceeds $V_{OFD(ON)}$, a state of top fault detection occurs, and an error flag is output.



Application Example



Selection of Components Externally Connected

| Symbol | Value | Purpose |
|--|--------|---|
| R _{IN1} , R _{C_{SB}} , R _{SI} , R _{SCLK} , R _{SO} | 1 kΩ | Register for microcontroller protection against negative voltage surge. |
| R _{RX} , R _{TX} | 1 kΩ | Register for microcontroller protection against negative voltage surge. |
| R _{KIO} | 480 Ω | KIO Pull-up Resistor |
| C _{VX} | 0.1 μF | Capacitor for noise rejection on power supply lines ^(Note 1) |
| C _{VS} | 0.1 μF | Capacitor for noise rejection on power supply lines ^(Note 1) |
| C _{V50} | 220 μF | LDO Output Capacitor ^{(Note 1)(Note 2)} |
| C _{V502} | 0.1 μF | LDO Output Capacitor ^{(Note 1)(Note 3)} |
| Z _{OUT1} | - | Zener diode for the reverse energy absorption when inductive load is turned off ^(Note 4) |

^(Note 1) It is recommended to insert capacitors as close as possible between VX and PGND, between VS and AGND, and between V50 and AGND.

^(Note 2) Connect large capacitor to stabilize the output.

^(Note 3) When using a capacitor with ESR of 1 Ω or more in C_{V50}, insert a ceramic capacitor (C_{V502}) in parallel.

^(Note 4) Connect it when driving an inductive load that exceeds active clamp energy of this product. The same is true for OUT2 to OUT5.

I/O Equivalence Circuits

| Pin No. | Pin Name | I/O Equivalence Circuit |
|---------|----------|-------------------------|
| 1 | VS | |
| 2 | IN1 | |
| 3 | V5O | |
| 4 | AGND | - |
| 5 | CSB | |
| 6 | SCLK | |
| 7 | SI | |
| 8 | SO | |

I/O Equivalence Circuits – continued

| Pin No. | Pin Name | I/O Equivalence Circuit |
|---------|----------|-------------------------|
| 9 | RX | |
| 10 | TX | |
| 11 | KIO | |
| 12 | VX | |
| 13 | OUT5 | |
| 14 | OUT4 | |
| 15 | OUT3 | |
| 16 | PGND | |
| 17 | OUT2 | |
| 18 | OUT1 | |
| 19 | OUT1 | |
| 20 | PGND | |

Operational Notes

1. Reverse Connection of Power Supply

Connecting the power supply in reverse polarity can damage the IC. Take precautions against reverse polarity when connecting the power supply, such as mounting an external diode between the power supply and the IC's power supply pins.

2. Power Supply Lines

Design the PCB layout pattern to provide low impedance supply lines. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

3. Ground Voltage

Ensure that no pins are at a voltage below that of the ground pin at any time, even during transient condition.

4. Ground Wiring Pattern

When using both small-signal and large-current ground traces, the two ground traces should be routed separately but connected to a single ground at the reference point of the application board to avoid fluctuations in the small-signal ground caused by large currents. Also ensure that the ground traces of external components do not cause variations on the ground voltage. The ground lines must be as short and thick as possible to reduce line impedance.

5. Recommended Operating Conditions

The function and operation of the IC are guaranteed within the range specified by the recommended operating conditions. The characteristic values are guaranteed only under the conditions of each item specified by the electrical characteristics.

6. Inrush Current

When power is first supplied to the IC, it is possible that the internal logic may be unstable and inrush current may flow instantaneously due to the internal powering sequence and delays, especially if the IC has more than one power supply. Therefore, give special consideration to power coupling capacitance, power wiring, width of ground wiring, and routing of connections.

7. Testing on Application Boards

When testing the IC on an application board, connecting a capacitor directly to a low-impedance output pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from the test setup during the inspection process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.

8. Inter-pin Short and Mounting Errors

Ensure that the direction and position are correct when mounting the IC on the PCB. Incorrect mounting may result in damaging the IC. Avoid nearby pins being shorted to each other especially to ground, power supply and output pin. Inter-pin shorts could be due to many reasons such as metal particles, water droplets (in very humid environment) and unintentional solder bridge deposited in between pins during assembly to name a few.

9. Unused Input Pins

Input pins of an IC are often connected to the gate of a MOS transistor. The gate has extremely high impedance and extremely low capacitance. If left unconnected, the electric field from the outside can easily charge it. The small charge acquired in this way is enough to produce a significant effect on the conduction through the transistor and cause unexpected operation of the IC. So unless otherwise specified, unused input pins should be connected to the power supply or ground line.

Operational Notes – continued

10. Regarding the Input and Output Pins of the IC

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of the P layers with the N layers of other elements, creating a parasitic diode or transistor. For example (refer to figure below):

When $GND > Pin A$ and $GND > Pin B$, the P-N junction operates as a parasitic diode.

When $GND > Pin B$, the P-N junction operates as a parasitic transistor.

Parasitic diodes inevitably occur in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Therefore, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.

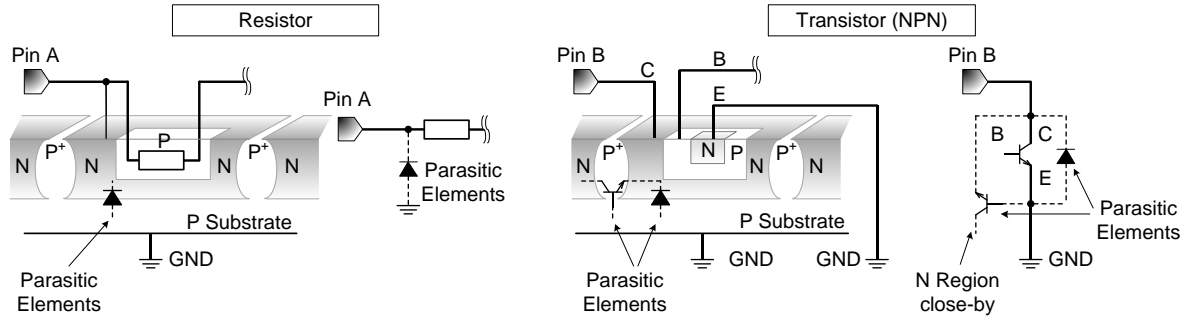


Figure 66. Example of Monolithic IC Structure

11. Ceramic Capacitor

When using a ceramic capacitor, determine a capacitance value considering the change of capacitance with temperature and the decrease in nominal capacitance due to DC bias and others.

12. Thermal Shutdown Function (TSD)

This IC has a built-in thermal shutdown function that prevents heat damage to the IC. Normal operation should always be within the IC's maximum junction temperature rating. If however the rating is exceeded for a continued period, the junction temperature (T_j) will rise which will activate the TSD function that will turn OFF power output pins. When the T_j falls below the TSD threshold, the circuits are automatically restored to normal operation.

Note that the TSD function operates in a situation that exceeds the absolute maximum ratings and therefore, under no circumstances, should the TSD function be used in a set design or for any purpose other than protecting the IC from heat damage.

13. Over Current Protection Function (OCP)

This IC incorporates an integrated overcurrent protection function that is activated when the load is shorted. This protection function is effective in preventing damage due to sudden and unexpected incidents. However, the IC should not be used in applications characterized by continuous operation or transitioning of the protection function.

14. Active Clamp Operation

The IC integrates the active clamp function to internally absorb the reverse energy E_L which is generated when the inductive load is turned off. When the active clamp operates, the thermal shutdown function does not work. Decide a load so that the reverse energy E_L is active clamp tolerance E_{AS} (refer to Figure 1.2.) or under when inductive load is used.

Operational Notes – continued

15. Power Supply Step Fluctuation

If the voltage of the power supply pin (VS) falls sharply, the output pin (OUT) may temporarily turn off as shown in Figure 67. If the power supply pin is expected to fall sharply, take measures such as inserting a capacitor between the power supply pin and the ground pin so that it falls within the recommended usage range shown in Figure 68.

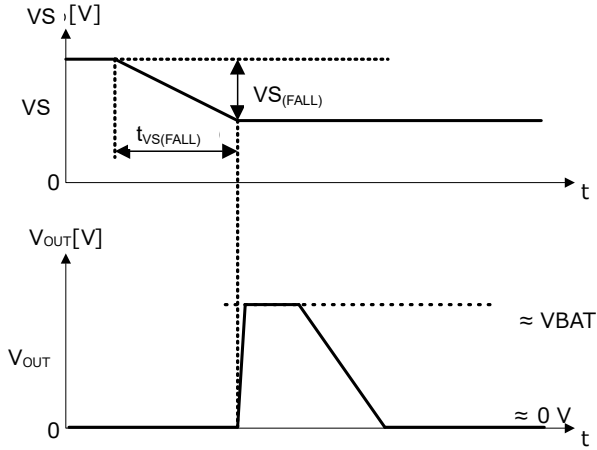


Figure 67. Output OFF operation when power supply fluctuates sharply

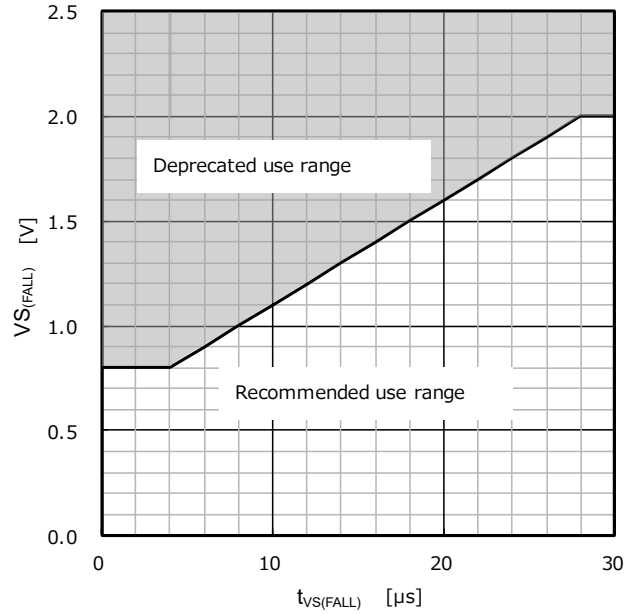


Figure 68. Recommended use range

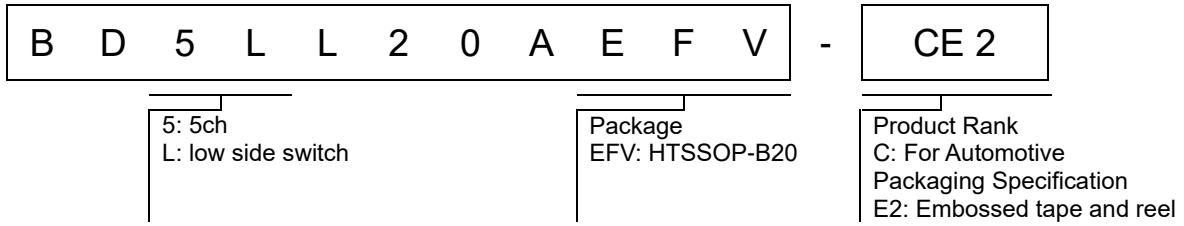
16. GND Pin Connection

Connect all ground pins to ground.

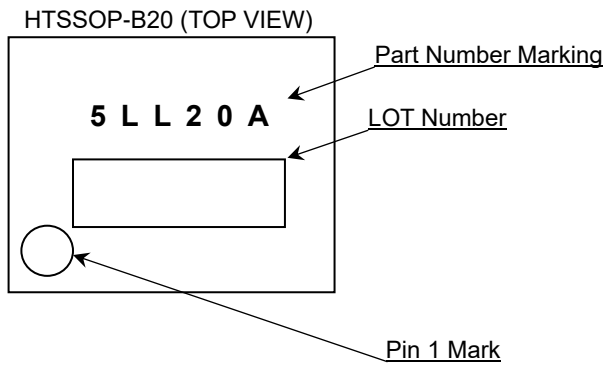
17. Same Pin Connection

Connect all OUT1 pins to same line.

Ordering Information

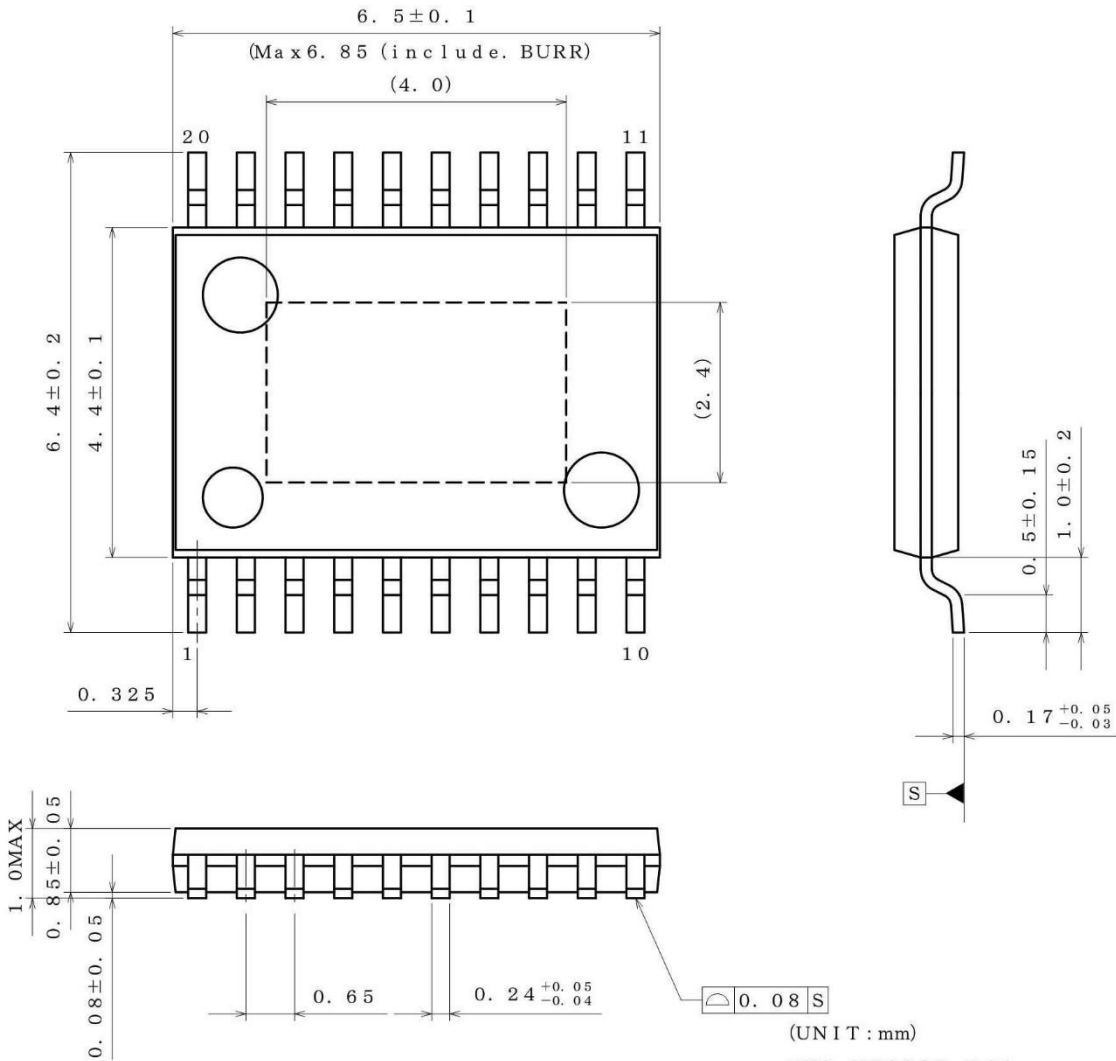


Marking Diagram



Physical Dimension and Packing Information

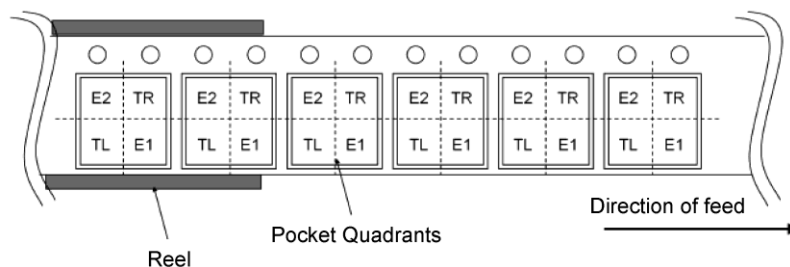
| | |
|--------------|------------|
| Package Name | HTSSOP-B20 |
|--------------|------------|



(UNIT : mm)
 PKG : HTSSOP-B20
 Drawing No. EX192-5002

< Tape and Reel Information >

| | |
|-------------------|---|
| Tape | Embossed carrier tape |
| Quantity | 2500pcs |
| Direction of feed | E2 The direction is the pin 1 of product is at the upper left when you hold reel on the left hand and you pull out the tape on the right hand |



Revision History

| Date | Revision | Changes |
|-------------|----------|-------------|
| 13.Jan.2023 | 001 | New Release |

Notice

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1. If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment ^(Note 1), aircraft/spacecraft, nuclear power controllers, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

(Note1) Medical Equipment Classification of the Specific Applications

| JAPAN | USA | EU | CHINA |
|-----------|-----------|------------|-----------|
| CLASS III | CLASS III | CLASS II b | CLASS III |
| CLASS IV | | CLASS III | |

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 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (Exclude cases where no-clean type fluxes is used. However, recommend sufficiently about the residue.); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
4. The Products are not subject to radiation-proof design.
5. Please verify and confirm characteristics of the final or mounted products in using the Products.
6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
8. Confirm that operation temperature is within the specified range described in the product specification.
9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

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 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
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4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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